G. PULLA REDDY ENGINEERING COLLEGE (Autonomous): KURNOOL Accredited by NBA of AICTE and NAAC of UGC An ISO 9001:2008 Certified Institution Affiliated to JNTUA, Anantapur



Scheme – 2017 B.Tech I and II Semester Syllabus G. Pulla Reddy Engineering College (Autonomous): Kurnool Accredited by NBA of AICTE and NAAC of UGC Affiliated to JNTUA, Anantapuramu

FOUR YEAR B.Tech DEGREE COURSE Scheme of instruction and Examination (Effective from 2017-18)

	I/II Semester								Scheme: 2	2017
S.No ·	Subject	Code	Credits	In	cheme struct riods/ k	tion	Duration of End Exam (Hours)	Exa	Scheme of amination N Marks	/Iax
				L	D/T	Р		End Exam	Internal Assessment	Total
Ι	Theory									
1	Engineering Mathematics- I / II	BS101/ BS102	3	2	1	-	3	60	40	100
2	Computer Programming / Data Structures	CS101/ CS103	3	3	-	-	3	60	40	100
3	Professional Communication and English – I / II	HU101/ HU102	3	3	-	-	3	60	40	100
4	Applied Physics	BS103	3	2	1	-	3	60	40	100
5	Engineering Chemistry	BS105	3	3	-	-	3	60	40	100
6	Engineering Drawing	ME101	3	-	3	-	3	60	40	100
II	Practicals									
7	Computer Programming Lab	CS102	1	-	-	2	3	50	50	100
8	Applied Physics Lab	BS104	1	-	-	2	2	50	50	100
9	Engineering Chemistry Lab	BS106	1	-	-	2	2	50	50	100
	Total		21	13	5	6		510	390	900

I/II Semester

S.No Subject Code Credits Scheme of Duration Scheme of Instruction of End **Examination Max Periods/Wee** Exam Marks k (Hours) End Internal Total D/T L Р Exam Assessment Ι Theory Engineering Mathematics- I / II BS101/ 3 2 3 60 40 100 1 1 _ BS102 2 Computer Programming / CS101/ 3 3 3 60 40 100 _ -CS103 Data Structures 3 HU101/ 3 Professional Communication 3 3 60 40 100 --HU102 and English – I / II 4 EE101 3 2 1 3 60 40 100 Elements of Electrical -Engineering EC101 5 3 2 1 3 60 40 100 Basic Electronics Engineering -CE101 3 2 3 40 100 6 **Engineering Mechanics** 1 60 -Practicals Π 7 Data Structures Lab CS104 2 3 50 50 100 1 _ -8 HU103 2 Phonetics & Communication 1 2 50 50 100 _ _ Skills Lab ME102 2 3 9 Engineering Workshop 1 -_ 50 50 100 21 510 390 900 Total 14 4 6

Scheme: 2017

<u>FOUR YEAR B.Tech DEGREE COURSE</u> Scheme of instruction and Examination (Effective from 2017-18) (For ME, EEE, CE)

	I Semester								Scheme: 2	017
S.No ·	Subject	Code	Credits	In	cheme struct iods/V	ion	Duration of End Exam	Exa	Scheme of amination N Marks	
				L	D/T	Р	(Hours)	End Exam	Internal Assessment	Total
Ι	Theory									
1	Engineering Mathematics – I	BS101	3	2	1	-	3	60	40	100
2	Computer Programming	CS10 1	3	3	-	-	3	60	40	100
3	Professional Communication and English – I	HU10 1	3	3	-	-	3	60	40	100
4	Applied Physics	BS103	3	2	1	-	3	60	40	100
5	Engineering Chemistry	BS105	3	3	-	-	3	60	40	100
6	Engineering Drawing	ME10 1	3	-	3	-	3	60	40	100
Π	Practicals									
7	Computer Programming Lab	CS102	1	-	-	2	3	50	50	100
8	Applied Physics Lab	BS104	1	-	-	2	2	50	50	100
9	Engineering Chemistry Lab	BS106	1	-	-	2	2	50	50	100
	Total		21	13	5	6		510	390	900

II Semester

Scheme: 2017

S.No	Subject	Code	Credits	S	cheme	e of	Duration		Scheme of	
•				In	struct	tion	of End	Ex	amination N	I ax
				Per	iods/V	Neek	Exam		Marks	
				L	D/T	Р	(Hours)	End Exam	Internal Assessment	Total
Ι	Theory									
1	Engineering Mathematics – II	BS102	3	2	1	-	3	60	40	100
2	Data Structures	CS10 3	3	3	-	-	3	60	40	100
3	Professional Communication and English – II	HU10 2	3	3	-	-	3	60	40	100
4	Elements of Electrical Engineering	EE101	3	2	1	-	3	60	40	100
5	Basic Electronics Engineering	EC101	3	2	1	-	3	60	40	100
6	Engineering Mechanics	CE101	3	2	1	-	3	60	40	100
II	Practicals									
7	Data Structures Lab	CS104	1	-	-	2	3	50	50	100
8	Phonetics & Communication Skills Lab	HU10 3	1	-	-	2	2	50	50	100
9	Engineering Workshop	ME10 2	1	-	-	2	3	50	50	100
	Total		21	14	4	6		510	390	900

FOUR YEAR B.Tech DEGREE COURSE Scheme of instruction and Examination (Effective from 2017-18) (For CSE, ECE)

	I Semester								Scheme: 2	017
S.No	Subject	Code	Credits	In	cheme struct iods/V	ion	Duration of End Exam	Exa	Scheme of amination N Marks	
				L	D/T	Р	(Hours)	End Exam	Internal Assessment	Total
Ι	Theory									
1	Engineering Mathematics – I	BS101	3	2	1	-	3	60	40	100
2	Computer Programming	CS10 1	3	3	-	-	3	60	40	100
3	Professional Communication and English – I	HU10 1	3	3	-	-	3	60	40	100
4	Elements of Electrical Engineering	EE101	3	2	1	-	3	60	40	100
5	Basic Electronics Engineering	EC101	3	2	1	-	3	60	40	100
6	Engineering Mechanics	CE101	3	2	1	-	3	60	40	100
II	Practicals									
7	Computer Programming Lab	CS102	1	-	-	2	3	50	50	100
8	Phonetics & Communication Skills Lab	HU10 3	1	-	-	2	2	50	50	100
9	Engineering Workshop	ME10 2	1	-	-	2	3	50	50	100
	Total		21	14	4	6		510	390	900

	II Semester								Scheme: 2	2017
S.No	Subject	Code	Credits		cheme struct	-	Duration of End	Ex	Scheme of amination N	
				Per	iods/V	Veek	Exam		Marks	
				L	D/T	Р	(Hours)	End Exam	Internal Assessment	Total
Ι	Theory									
1	Engineering Mathematics – II	BS102	3	2	1	-	3	60	40	100
2	Data Structures	CS10 3	3	3	-	-	3	60	40	100
3	Professional Communication and English – II	HU10 2	3	3	-	-	3	60	40	100
4	Applied Physics	BS103	3	2	1	-	3	60	40	100
5	Engineering Chemistry	BS105	3	3	-	-	3	60	40	100
6	Engineering Drawing	ME10 1	3	-	3	-	3	60	40	100
Π	Practicals									
7	Data Structures Lab	CS104	1	-	-	2	3	50	50	100
8	Applied Physics Lab	BS104	1	-	-	2	2	50	50	100
9	Engineering Chemistry Lab	BS106	1	-	-	2	2	50	50	100
	Total		21	13	5	6		510	390	900

ENGINEERING MATHEMATICS – I (EM1)

Common		1	anch					cheme : 2017
Course Code	Category	Hou	rs/Wo	eek	Credits	Ν	Iaximum M	arks
BS101	Foundation	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
		2	1	-	3	40	60	100
Sessional	Exam Duratio	$\mathbf{n}:2$	Hrs			End H	Exam Durat	ion: 3 Hrs
<u> </u>	A 4	1 (1			
	comes : At the				idents will	be able to		
	e first order dif				differentie	1 aquations and	thair applia	ations in solvin
	ineering proble		i ingn	er order	unierentia	ii equations and	i then applie	ations in solvin
			nge's	mean va	alue theore	ms. Apply parti	al derivative	es to study
						niques and eval		
	grals.		11	5 0		1		1
						to solve different		
CO5: Und	erstand gradier	nt, dive	ergent	, curl. A	Apply Gree	en's, Stoke's an	d Gauss-dive	ergence theorem
to ev	valuate line, sui	rface a	and vo	lume int	tegrals.			
Differential					UNIT - I			
				of coo	ling, law o			and Non- linea
				U	J NIT - II			
	D'CC (11)	-	•					
	r Differential l is linear differe					higher order wit	th constant c	oefficients, Nor
Homogeneou	s linear differe	ential e	equation	ons of se	econd and			oefficients, Nor
Homogeneou homogeneou	s linear differe	ential e	equation	ons of se	econd and			
Homogeneou homogeneou	s linear differe	ential e	equation	ons of se ^{ax} , sin ax	econd and			
Homogeneou homogeneou C-R circuits.	is linear differe s term of the ty <i>Calculus</i>	pential ϵ	$equation (x) = e^{-1}$	ons of se ^{ax} , sin ax U	econd and \mathbb{I} $x, x^n, e^{ax}v(x)$ NIT - III	(x, xv(x)) and Ge	neral case. A	pplications to I
Homogeneou homogeneou C-R circuits. Differential Rolle's theor	s linear differe s term of the ty Calculus em, Lagrange's	pential ϵ	$equation (x) = e^{-1}$	ons of se ^{ax} , sin ax U	econd and \mathbb{I} $x, x^n, e^{ax}v(x)$ NIT - III		neral case. A	pplications to I
Homogeneou homogeneou C-R circuits. Differential Rolle's theor Multiple Inte	s linear differe s term of the ty Calculus em, Lagrange's ggrals	ential e $ppe f(x)$	equation $x = e^{-1}$	ons of se ^{ax} , sin ax U e theorem	econd and 1 r, x ⁿ , e ^{ax} v(x <mark>NIT - III</mark> m. Maxima	(x, xv(x)) and Ge and minima of	neral case. A	pplications to I
Homogeneou homogeneou C-R circuits. Differential Rolle's theor Multiple Inte Double integ	s linear differe s term of the ty Calculus em, Lagrange's grals rals, change o	reperies mean	equation $x = e^{-1}$	ons of se ^{ax} , sin ax U e theorem ntegration	econd and \mathbb{R} , x^n , $e^{ax}v(x)$ NIT - III m. Maximation, Change	(x), $xv(x)$ and Ge a and minima of to polar coord	neral case. A	pplications to I
Homogeneou homogeneou C-R circuits. Differential Rolle's theor Multiple Inte Double integ	s linear differe s term of the ty Calculus em, Lagrange's ggrals	reperies mean	equation $x = e^{-1}$	ons of set ax, sin $axUe theoremntegrationume by t$	econd and 1 $x, x^n, e^{ax}v(x)$ NIT - III m. Maxima on, Change riple integr	(x), $xv(x)$ and Ge a and minima of to polar coord	neral case. A	pplications to I
Homogeneou homogeneou C-R circuits. Differential Rolle's theor Multiple Inte Double integr	s linear differe s term of the ty Calculus em, Lagrange's ggrals rals, change o ation. Triple in	reperies mean	equation $x = e^{-1}$	ons of set ax, sin $axUe theoremntegrationume by t$	econd and \mathbb{R} , x^n , $e^{ax}v(x)$ NIT - III m. Maximation, Change	(x), $xv(x)$ and Ge a and minima of to polar coord	neral case. A	pplications to I
Homogeneou homogeneou C-R circuits. Differential Rolle's theor Multiple Inte Double integ double integr	s linear differe s term of the ty Calculus em, Lagrange's grals rals, change o ation. Triple in usforms	$f(x) = \frac{1}{2}$	equation $x = e^{-1}$	ons of set a^x , sin ax U e theorem ntegration ume by t U	econd and 1 $x, x^n, e^{ax}v(x)$ NIT - III m. Maxima on, Change riple integri NIT - IV	(x), $xv(x)$ and Generation (x), $xv(x)$ and Generation (x), $xv(x)$ and $Generation(x), xv(x) and Generation(x), xv(x) and $	neral case. A	pplications to I
Homogeneou homogeneou C-R circuits. Differential of Rolle's theor Multiple Inte Double integ double integr Laplace Tran Laplace tran	s linear differe s term of the ty Calculus em, Lagrange's grals, change of ation. Triple in usforms sform of stand	s mear f orde lard f	equation $x = e^{-1}$	ons of set ax, sin $axue theoremntegrationume by tuons, first$	econd and 1 $x, x^n, e^{ax}v(x)$ NIT - III m. Maxima on, Change riple integr NIT - IV x second	(x, xv(x)) and Ge and minima of to polar coord cals.	functions of dinates. Area	Explications to I Explications to I Explications to I Explications to I The section of the secti
Homogeneou homogeneou C-R circuits. Differential Rolle's theor Multiple Inte Double integr double integr Laplace Tran Laplace tran derivatives,	s linear differe s term of the ty <i>Calculus</i> em, Lagrange's ggrals rals, change o ation. Triple in <i>usforms</i> sform of stand integrals, mult	s mear f orde tegral	equation $x) = e^{-1}$ x = 1 x = 1	ons of se ax, sin ax U e theorem ntegration ume by t U ons, first oy t, div	econd and 1 $x, x^n, e^{ax}v(x)$ NIT - III m. Maxima on, Change riple integr NIT - IV x second vision by	(x, xv(x)) and Generation a and minima of the topolar coord rals. the shifting theory that and periodic	rems, Laplac	The production of the production of the product of
Homogeneou homogeneou C-R circuits. Differential of Rolle's theor Multiple Integ double integ double integr Laplace Tran Laplace tran derivatives, transforms,	s linear differe s term of the ty <i>Calculus</i> em, Lagrange's ggrals rals, change o ation. Triple in <i>usforms</i> sform of stand integrals, mult	s mear f orde tegral	equation $x) = e^{-1}$ x = 1 x = 1	ons of se ax, sin ax U e theorem ntegration ume by t U ons, first oy t, div	econd and 1 $x, x^n, e^{ax}v(x)$ NIT - III m. Maxima on, Change riple integr NIT - IV x second vision by	(x, xv(x)) and Generation a and minima of the topolar coord rals. the shifting theory that and periodic	rems, Laplac	pplications to I
Homogeneou homogeneou C-R circuits. Differential of Rolle's theor Multiple Integ double integ double integr Laplace Tran Laplace tran derivatives, transforms,	s linear differe s term of the ty <i>Calculus</i> em, Lagrange's ggrals rals, change o ation. Triple in <i>usforms</i> sform of stand integrals, mult	s mear f orde tegral	equation $x) = e^{-1}$ x = 1 x = 1	ons of se ax, sin ax U e theorem th	econd and \mathbb{R} , x^n , $e^{ax}v(x)$ NIT - III m. Maxima on, Change riple integr NIT - IV \mathbb{R} second vision by ons of La	(x, xv(x)) and Generation a and minima of the topolar coord rals. the shifting theory that and periodic	rems, Laplac	The production of the production of the product of
Homogeneou homogeneou C-R circuits. Differential Rolle's theor Multiple Inte Double integ double integr Laplace Tran Laplace tran derivatives, transforms, equations.	s linear differe s term of the ty Calculus em, Lagrange's grals, change o ation. Triple in <i>isforms</i> sform of stand integrals, mult Convolution T	s mear f orde tegral	equation $x) = e^{-1}$ x = 1 x = 1	ons of se ax, sin ax U e theorem th	econd and 1 $x, x^n, e^{ax}v(x)$ NIT - III m. Maxima on, Change riple integr NIT - IV x second vision by	(x, xv(x)) and Generation a and minima of the topolar coord rals. the shifting theory that and periodic	rems, Laplac	The production of the production of the product of
Homogeneou homogeneou C-R circuits. Differential of Rolle's theor Multiple Integ double integr Laplace Tran Laplace tran derivatives, transforms, equations. Vector Calcu Scalar and V Repeated op	<i>Calculus</i> em, Lagrange's em, Lagrange's grals rals, change o ation. Triple in <i>isforms</i> sform of stance integrals, mult Convolution T	s mear f orde tegral lard f iplicat Theore	equation $x) = e^{-1}$ $x = e^{-1}$	ons of se ax, sin ax U e theorem ntegration ume by t U ons, first oy t, div application theorem	econd and \mathbb{I} $x, x^n, e^{ax}v(x)$ NIT - III m. Maxima on, Change riple integr NIT - IV x second vision by ons of La JNIT - V xe, curl, gr	(x, xv(x)) and Generation a and minima of the topolar coord rals. the shifting theory that and periodic	rems, Laplac functions of dinates. Area rems, Laplac functions. ms to ordin	The production of the production of the product of

Text Books :

- 1. B.S. Grewal- Higher Engineering Mathematics. Khanna Publishers, 42nd Edition, 2012.
- 2. T.K.V.Iyengar and others -A Text Book of Engineering Mathematics, Vol 1-S.Chand & Company, 13th Edition 2014.

Reference Books :

- 1. B.V. Ramana -Higher Engineering Mathematics, TMH Publishers, 2nd Edition, 2006.
- 2. N.P.Bali and others -A Text Book of Engineering Mathematics, Lakshmi publishers, 7th Edition, 2009.
- 3. Erwyn Kreyszig Advanced Engineering Mathematics, John wiley, 8th Edition 2006.

Question Paper Pattern:

Sessional Exam

The question paper for sessional examination is for 30 marks, covering half of the syllabus for first sessional and remaining half for second sessional exam. Question No 1 which carries 6 marks contains three short answer questions of two marks each. The remaining three questions shall be EITHER/OR type questions carrying 8 marks each

End Exam

COMPUTER PROGRAMMING (CP)

	ommon for all I	1				1		ne: 2017
Course Code	Category	Hou	rs/We	ek	Credits		ximum Marks	T
CS101	Foundation	L	T	Р	С	Continuous Internal Assessment	End Exam	ΤΟΤΑΙ
		3	0	-	3	40	60	100
Sessional Ex	am Duration : 2	2 Hrs				End E	xam Duration	3 Hrs
<u> </u>	A (1	1 6.1			1 4 111	11 /		
	omes : At the end							
v	an algorithm and					m.		
	arize the structur n the use of Arra			-	nogram.			
	ate the application	•			nointers			
	stand the purpose				-			
	stand the purpose		ucture	s anu i	lies in C.			
				TINI	T – I			
Fundamentals	of Computers			0111				
	of a Computer,	Type	s of P	rogran	nming langu	ages, Algorith	m- Characteris	tics of a
	charts and Exan			÷	2 0			
C Fundamenta								
Identifiers and	Key words, Data	а Туре	es, Cor	istants	and Variab	ole declarations	, Operators, Ex	pressions
Header files.								
Data input/out	nut			UNI	T – II			
printf(), scanf() Flow Control Selection- if s	, getchar(), putch tatements, switc			outs();	Type conve	-	-	or; break
printf(), scanf() Flow Control	, getchar(), putch tatements, switc			outs(); , goto	Type conve	-	-	or; break
<i>Flow Control</i> Selection- if s continue, nested	, getchar(), putch tatements, switc			outs(); , goto	Type conve statement.	-	-	or; break
printf(), scanf() Flow Control Selection- if s continue, nested Arrays Declaring and Character array operations. Functions Definition, Acc	, getchar(), putch tatements, switc	h stat	ension ctions	outs(); , goto UNI al and : strlen gument	Type conve statement. F – III d Two dim n(), strcpy() ts to a funct ion.	Loops- Whil nensional array , strcmp(), strc	e, do-while, for ys, Processing cat(). Examples	an array – Matrix
printf(), scanf() <i>Flow Control</i> Selection- if s continue, nested <i>Arrays</i> Declaring and Character array operations. <i>Functions</i> Definition, Acc static, register;	, getchar(), putch tatements, switc d loops. Initializing One rs, String handlin essing a function	h stat	ension ctions	outs(); , goto UNI al and : strlen gument	Type conve statement. F – III d Two dim n(), strcpy() ts to a funct	Loops- Whil nensional array , strcmp(), strc	e, do-while, for ys, Processing cat(). Examples	an array – Matrix
printf(), scanf() <i>Flow Control</i> Selection- if s continue, nested <i>Arrays</i> Declaring and Character array operations. <i>Functions</i> Definition, Acc static, register; <i>Pointers</i> Introduction to	, getchar(), putch tatements, switc d loops. Initializing One rs, String handlin essing a function	h star e dim ng fun n, pass ng arra	tement ension actions: ing arg ays to a laration	outs(); , goto <u>UNI</u> al and a strler ument funct <u>UNI</u> ns, Op nter; P	Type conversion statement. F – III d Two dimentification dimentification dimentification dimension	Loops- Whil nensional array , strcmp(), strc ion, storage cla pointers, Poir	e, do-while, for ys, Processing cat(). Examples asses: automatic	an array – Matrix , external s; Passing
printf(), scanf() <i>Flow Control</i> Selection- if s continue, nested <i>Arrays</i> Declaring and Character array operations. <i>Functions</i> Definition, Acc static, register; <i>Pointers</i> Introduction to address to a fun	, getchar(), putch tatements, switc l loops. Initializing One rs, String handlin essing a function Recursion, Passir pointers, Pointe ction; Function r	h star e dim ng fun n, pass ng arra	tement ension actions: ing arg ays to a laration	outs(); , goto <u>UNI</u> al and a strler ument funct <u>UNI</u> ns, Op nter; P	Type conversion statement. F – III d Two dimention dimention (), strepy() ts to a function. F – IV perations on	Loops- Whil nensional array , strcmp(), strc ion, storage cla pointers, Poir	e, do-while, for ys, Processing cat(). Examples asses: automatic	an array – Matrix , external s; Passing
printf(), scanf() Flow Control Selection- if s continue, nested Arrays Declaring and Character array operations. Functions Definition, Acc static, register; Pointers Introduction to address to a fun Structures and Defining a stru	, getchar(), putch tatements, switc l loops. Initializing One rs, String handlin essing a function Recursion, Passir pointers, Pointe ction; Function r	h stat e dim ng fun n, pass ng arra er dec eturni g a str	tement ension actions: ing arg ays to a laration ng Poin ucture,	outs(); , goto <u>UNI'</u> al and : strler ument tfunct <u>UNI'</u> ns, Op <u>unter; P</u> <u>UNI</u>	Type conve statement. $\Gamma - III$ d Two dim n(), strcpy() ts to a funct ion. $\Gamma - IV$ berations on ointer to a f T - V tures and po	Loops- Whil nensional array , strcmp(), strc ion, storage cla pointers, Poir unction, Dynam	e, do-while, fa vs, Processing cat(). Examples asses: automatic nters and arrays nic Memory All	an array – Matri , external s; Passing location.

Text Books :

- 1. Ron S.Gottfried, Programming with C, (TMH Schuam Outline Series) 3rd Edition -2011.
- 2. B.W. Kernignan and Dennis M.Ritchie, The C Programming Language, (PHI), 2nd Edition 2003.

Reference Books :

- 1. E.Balaguruswamy, Programming in ANSI C, TMH, 2003.
- 2. Yashavanth P.Kanetkar, Let US C, BPB Publications, 7th Edition, 2007.
- 3. Ajay Mittal, Programming in C, Pearson Education, 2010.

Web References:

- 1. https://www.tutorialspoint.com/cprogramming/c_program_structure.htm
- 2. http://fresh2refresh.com/c-programming/c-basic-program/

Question Paper Pattern:

Sessional Exam

The question paper for sessional examination is for 30 marks, covering half of the syllabus for first sessional and remaining half for second sessional exam. Question No 1 which carries 6 marks contains three short answer questions of two marks each. The remaining three questions shall be EITHER/OR type questions carrying 8 marks each

End Exam

Semester :	Common for a	ll Bra	nches	5			Sch	eme : 2017
Course Code	Category	Hou	rs/W	eek	Credits	Ν	Maximum Ma	rks
HU101	Foundation	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
		3	-	-	3	40	60	100
Sessional	Exam Duration	: 2 H	rs			End	Exam Duration	n: 3 Hrs
CO 1: Use C CO 2: Use a CO 3: Comp Scan		ceptab oulary and Te	ole En in Teo echnic	glish i chnica al Coi	n Oral and Il and Gene ntent using	Written commu ral Contexts. various Readin	g Skills like Sk	-
CO 4: Write and	Functional Lette Persuasive nature		mmar	ies an	d Essays of	topical, Narrat	ive, Descriptiv	e, Analytical
	re - Kailash Saty				UNIT – I			
Writing: Wri	ading with a purp ting notes and pa	aragraj	•		inderstandii UNIT – II	ng		
Vocabulary: Grammar: A A Reading: Ski	s Word - R K Na One-word substi dverbs, Verbs – V rticles, Word Or imming and Scan ctional Letters –	tutes, /erb fo der ning	orms,	Types tters, (of Verbs, I	Prepositions, Co	onjunctions and	1
				U	JNIT – III			
Vocabulary: Grammar: To Reading: Uso	, Stay Foolish - Prefixes and Suf enses, Concord, Y e of Dictionary, 7 e–Taking and No	fixes, Voices Γhesau	Homo and I irus, I	Report Library , Com	ted Speech and Interr	et for Informat	ion	
The Open W	indow – Saki(H	H Mu	nro)					
-	Words often Co		,	Colloc	ations			
Grammar: Q	uestion Tags, De	grees				ormation of Ser	ntences and	
C								
	ading Comprehe							

Detailed Study Text:

1. The Enriched Reading by D. Sudha Rani, Pearson India Education Services Pvt. Ltd, Second Impression, 2017.

Reference Books:

1. Michael Swan, Practical English Usage, Third Edition, OUP, 2006.

2. David Green, Contemporary English Grammar, Structure and Composition, Second Edition, Lakshmi Publications, 2015.

3. Oxford Advanced Learners Dictionary of Current English, OUP, 2015.

4. Meenakshi Raman and Sangeetha Sarma, Technical Communication Principles and Practice, 3rd Edition, OUP, 2015.

5. Raj N Bakshi, English Grammar Practice, Orient Blackswan, 2005.

Question Paper Pattern:

Sessional Exam

I Sessional Examination : 30 Marks

- 1. Essay Type Question 8 Marks
- 2. Short Answer Questions 8 Marks
- 3. Vocabulary 4 Marks
- 4. Grammar 5 Marks
- 5. Letter Writing 5 Marks

II Sessional Examination : 30 Marks

- 1. Essay Type Question 8 Marks
- 2. Short Answer Questions 8 Marks
- 3. Vocabulary 4 Marks
- 4. Grammar 6 Marks
- 5. Reading Comprehension 4 Marks

End Exam

- 1. Essay Type Question 10 Marks
- 2. Short Answer Questions 8 Marks
- 3. Vocabulary 12 Marks
- 4. Grammar 10 Marks
- 5. Reading Comprehension 10 Marks
- 6. Letter Writing 10 Marks

APPLIED PHYSICS (AP)

I /II Sei	mester: Common fo	or all l	Branc	hes			Scheme :	2017
Cours	se Category	Ηοι	irs/W	eek	Credits	Maximum	Marks	
Code	e							
BS10	3 Foundation	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
		2	1	-	3	40	60	100
Sessi	onal Exam Duration	: 2 H	rs			End Exam Du	ration: 3 H	Irs
Cours	se Outcomes : At the	end o	f the c	ourse	e students v	vill be able to		
CO1:	Understand the diffe	rent cr	ystal s	syster	ns, crystal	planes and determination	of the Cry	stal
			•	•		pplications of ultrasonic	•	
	of velocity of ultrasc	nic wa	ves ir	i liqu	ids.			
CO2:	Understand the phen	omend	on of i	nterfe	erence, diff	raction and their applicat	ions	
CO3:						soft and hard magnetic m		
	0		0		•	lessiner and Josephso		and of
CO4:	Understand different optical fibers, losses	+				ers and their applications, coptical fibers.	different t	ypes of
CO5:	Properties, synthesis	, appli	cation	s of N	Vanomateri	als and Carbon Nanotube	es.	

UNIT – I

Crystallography

Space lattice, Unit cell, Crystal systems, Miller Indices, Bravais Lattices, Interplanar Distance (without derivation), Number of atoms per unit cell, Coordination Number, Atomic Radius, Packing Factor for SC, BCC and FCC. Bragg's law, Bragg's X ray Spectrometer, Structural determination by Laue method, Powder method.

Ultrasonics

Introduction, Properties of ultrasonics, Production of ultrasonics by Magnetostriction method, Piezoelectric method, Detection of ultrasonics, Determination velocity of ultrasonics in liquids. Applications: SONAR, NDT, general applications.

Interference

UNIT – II

Introduction, Conditions for interference, Interference due to thin uniform film, wedge shaped film, Newton's rings. Applications of interference – Testing of flatness, determination of wavelength, radius of curvature, refractive index of liquid, Non-reflective coatings.

Diffraction

Introduction, Fraunhoffer diffraction due to single slit, double slit, grating, circular aperture (qualitative analysis only), Determination of wavelength using grating, Resolving power, Rayleigh's criterion for resolution, Resolving power of grating and telescope.

UNIT – III

Magnetic Materials

Origin of magnetism, permeability, susceptibility, Hysteresis, soft and hard magnetic materials and their applications, Ferrites: introduction, properties and applications.

Superconductivity

Introduction, properties and applications of superconductors, flux quantization, Meissner effect, Type-I and Type-II Superconductors, high temperature superconductors, Josephson effect, SQUIDS.

UNIT – IV

Lasers

Introduction, spontaneous and stimulated emission of radiation, characteristics of lasers, components of laser, Ruby, He-Ne, Nd-YAG and semiconductor lasers.

Fiber Optics

Principle and propagation of light in optical fibers, structure of optical fibers, types of optical fibers and their differences, Acceptance angle, Numerical aperture(NA), losses in optical fibers, fiber optic communication, fiber optic sensors.

UNIT – V

Nanomaterials

Introduction, Properties of nano particles, Synthesis by Ball Mill method, Sol-Gel method, CVD method, PVD method, Pulsed Laser Deposition method, Wire explosion method. Applications of nano materials

Carbon nano tubes

Carbon nano tubes: Classification, properties, Synthesis methods – Ball Mill method, CVD method, Arc method, Applications of carbon nano tubes, Effect of nanotechnology on environment.

Text Books :

- 1. M.N.Avadhanulu and P.G.Kshirsagar, A text Book of Engineering Physics, S.Chand & Company
- 2. V.Rajendran, Engineering Physics, McGraw Hill Education (India) Pvt Limited.
- 3. Dr. K.Vijaya Kumar, Engineering Physics, S.Chand & Company

Reference Books :

- 1. Hitendra K. Malik & A.K. Singh, Engineering Physics, Tata McGraw Hill Education Pvt. Ltd.
- 2. S.O. Pillai, Solid State Physics, New Age International Publications.
- 3. Francis A. Jenkins, Harvey E. White, Fundamentals of Optics, McGraw Hill International Editions.

Question Paper Pattern:

Sessional Exam

The question paper for sessional examination is for 30 marks, covering half of the syllabus for first sessional and remaining half for second sessional exam. Question No 1 which carries 6 marks contains three short answer questions of two marks each. The remaining three questions shall be EITHER/OR type questions carrying 8 marks each

End Exam

ENCINEERING CHEMISTRY (EC)

		E	NGIN	EER	ING CHE	MISTRY (EC)		
I / II Semeste	er: Common f	or all	Bran	ches			Sc	cheme : 2017
Course Code	Category	Hou	rs/We	eek	Credits	Ν	Maximum M	larks
BS105	Foundation	L 3	Т	Р	C 3	Continuous Internal Assessment 40	End Exam 60	TOTAL
Sossional	Exam Duration	-	- [rc	-	3	-	Exam Durat	
Sessionari		• 4 11	15					
CO1: Unders energy CO2: Describ associa CO3: Unders CO4: Judge t CO5: Unders <i>Electrochemia</i> Single electro numerical pr Electrochemia Fuel cells-H ₂ - Process of C corrosion, str concentration methods - Ca	tand the chemis istry & Corrosio ode potential- oblems. Electr cal energy syste O_2 Fuel cell. Co hemical & elec ress corrosion. corrosion and athodic protectio	t of el and e ality i ent. oncep al, pet try of Detern ochen ems – onduct troche Conce l pitt:	ectroc xplain ssues ts of p rol, di polyn minationical prima cometr emical entrationical entrationical entrationical entrationical	hemis s the offor stee for stee hase 1 esel a hers an ers an on. E series ary ba ic titra corro on ce prrosio	stry, disting concept of o eam generat rule and ref nd lubricar nd composi UNIT – I MF of a & its ap tteries – dr ations. osion and t ll corrosio on. Factor inhibitors.	uishes primary corrosion with j ion in the boile ractories. its. Understands ts. cell and its m oplications. Ele y cell, seconda heir mechanism n- differential s influencing	easurement, easurement, ectrolyte co ry batteries- ms. Galvanic aeration cor corrosion. (ethods.
dipping, and l	Electroplating o	fnick	el and					
Water Chemi	atm				UNIT – II			
Hardness of v of hardness Disadvantage foaming and colloidal cor	vater- Types, ex of water by E s of hard wate boiler corrosid	EDTA er-boi on. W extern	meth ler tro ater se	od, a oubles ofteni nditio	alkalinity & s-scale and ng method	dissolved ox sludge, caust s – internal co	xygen by W ic embrittler onditioning -	ter-Determinatio Vinkler's method ment, priming & - calgon process xchange process
Phase rule &	Refractories							
Terms involv component sy Pb-Ag system Refractory-cla	ved in phase ru vstem - water an n.	d sulp	ohur sy es- ro	stems efracters ns for	s. Condense oriness, re	ed phase rule-T	wo compone	pplication to on ent alloy systems thermal spalling
Fuels-Classifi fuels- Coal-p cracking-cata knocking-octa	proximate and proximate and proximate and provide the provided and provide the provided and provide the provide the provided and provid	ic valu ultima Synt esel- c	tte and thetic etane	alysis petro numb	. Liquid fo ol-Fischer-7 er. Prepara	uels-Petroleum- Tropsch's & I tion of biodies	Origin, Extr Bergius pro el. Gaseous f	calorimeter. Soli raction, Refining cess, Reforming fuels-Compositio on of volume an

mass of oxygen and air . Flue Gas Analysis by Orsat's Apparatus.

Lubricants- Classification of lubricants with examples. Definition and significance of the following characteristics of a good lubricating oil- viscosity, viscosity index, flash & fire point, acid number, saponifaction value, pour point and cloud point.

UNIT – V

Polymers & Composites

Fundamentals of addition & condensation polymerization with examples. Thermoplastic and Thermosetting plastics. Preparation, properties and uses of PVC, TEFLON, Nylons, Bakelite, Polyurethane. Rubber – Processing of latex. Drawbacks of natural rubber, vulcanization, properties of vulcanized rubber. Synthetic rubber- Buna S, Buna N, Silicone and Butyl Rubbers. Polymer composites – definition and uses of FRP - laminar composites.

Text Books :

1. P.C. Jain and Monika Jain, Engineering Chemistry, Dhanpat Rai and Sons, New Delhi 2010,15th edition.

Reference Books :

- 1. Shashi Chawla, A Reading of Engineering Chemistry, 3rd Edition, Dhanpat Rai and Co., New Delhi, 2011,3rd edition.
- Gowariker et al., Polymer Science and Technology, Prentice Hall of India Pvt. Ltd., New Delhi, 2004, 10th reprint.
- 3. Puri, Sharma and Pathania " Principles of Physical Chemistry". Vishal Publishing Co.,Jalandhar.1991,31st edition.
- 4. Kuriacose, J.C and Rajaram, J, Engineering Chemistry, Volume I/II, Tata McGraw Hill Publishing Co. Ltd. New Delhi, 2010, 2nd edition.
- 5. S.S.Dara, A Textbook of Engineering Chemistry, S. Chand & Co.Ltd. New Delhi, 2007,10th edition

Question Paper Pattern:

Sessional Exam

The question paper for sessional examination is for 30 marks, covering half of the syllabus for first sessional and remaining half for second sessional exam. Question No 1 which carries 6 marks contains three short answer questions of two marks each. The remaining three questions shall be EITHER/OR type questions carrying 8 marks each

End Exam

ENGINEERING DRAWING (ED)

	: Common f					1		heme : 2017
Course Code	Category	Hour	s/Wee	ek	Credits		ximum M	arks
ME101	Foundation	L	T	Р	С	Continuous Internal Assessment	End Exam	TOTAL
C I.F.		-	3	-	3	40	60	100
Sessional Ex	kam Duration	: 2 Hr	'S			End Exa	ım Durati	on: 3 Hrs
Course Outc	comes : At the	end of	the co	ourse s	students wil	be able to		
						and draw the pr	ojection of	f points, straight
	and planes	1	1 5		5	1	5	1 / 0
	projection of r							
						r surface develop	ments	_
	the orthograph			<u> </u>				
CO5: Draw	the isometric v	views fi	rom th	ne orth	ographic vi	ews		
					JNIT – I			
Introduction to	Fnainoorina	Drawi	ทลง					
	0 0		0	ring a	nd Dimensi	oning. Introductio	on to poly	ons and conics
Introduction to				-		oming. Introduction	on to polyg	gons and comes.
Orthographic p		I L'IIU	сланн	matio	115)			
Introduction, p	U U	rtions	nroiec	tions	of points F	inst angle projecti		tions of studiola
millouucion, p						insi anole mmech	on- Projec	unne ni eiraion
-					-	• • •	•	-
lines- parallel t	to one and inc				-	to both the plan	•	-
lines- parallel t simple problem	to one and inc as only)				-	• • •	•	-
lines- parallel t simple problem <i>Projection of p</i>	to one and inc as only) <i>lanes:</i>	lined t	o othe	er plar	ne- Inclined	to both the plan	es (treatme	ent is limited to
lines- parallel t simple problem <i>Projection of p</i> Regular planes	to one and inc as only) <i>lanes:</i> - perpendicula	elined t	o othe	er plar	ne- Inclined	• • •	es (treatme	ent is limited to
lines- parallel t simple problem <i>Projection of p</i>	to one and inc as only) <i>lanes:</i> - perpendicula	elined t	o othe	er plar one r	eference pla	to both the plan	es (treatme	ent is limited to
lines- parallel to simple problem <i>Projection of p</i> Regular planes Inclined to both	to one and inc as only) <i>lanes:</i> - perpendicula a the reference	elined t	o othe	er plar one r	ne- Inclined	to both the plan	es (treatme	ent is limited to
lines- parallel to simple problem <i>Projection of p</i> Regular planes Inclined to both <i>Projections of s</i>	to one and inc as only) <i>lanes:</i> - perpendicula a the reference solids:	r, para	llel to	er plar one r	ne- Inclined eference pla <u>NIT – II</u>	to both the plan	es (treatme	ent is limited to
lines- parallel to simple problem <i>Projection of p</i> Regular planes Inclined to both <i>Projections of s</i>	to one and inc as only) <i>lanes:</i> - perpendicula a the reference solids: right regular s	r, para	llel to	er plar one r	ne- Inclined eference pla <u>NIT – II</u>	to both the plan	es (treatme	ent is limited to
lines- parallel t simple problem <i>Projection of p</i> Regular planes Inclined to both <i>Projections of a</i> Projections of a	to one and inc as only) <i>lanes:</i> - perpendicula a the reference solids: right regular s	r, para	llel to	er plar one r U	ne- Inclined eference pla <u>NIT – II</u>	to both the plan	es (treatme	ent is limited to ference planes -
lines- parallel t simple problem <i>Projection of p</i> Regular planes Inclined to both <i>Projections of a</i> Projections of a	to one and inc as only) <i>lanes:</i> - perpendicula a the reference solids: right regular s both planes.	r, para	llel to	er plar one r U	ne- Inclined eference pla <u>NIT – II</u> nid, cylinde	to both the plan	es (treatme	ent is limited to ference planes -
lines- parallel to simple problem Projection of p Regular planes Inclined to both Projections of a and inclined to Sections of Sol	to one and inc as only) <i>lanes:</i> - perpendicula a the reference <i>solids:</i> right regular s both planes.	elined t r, para planes olids-	o othe	er plar one r U pyrar	ne- Inclined eference pla <u>NIT – II</u> mid, cylinde <u>NIT – III</u>	to both the plan	es (treatme to other re axis inclin	ent is limited to ference planes - ned to one plane
lines- parallel to simple problem Projection of p Regular planes Inclined to both Projections of a and inclined to Sections of Sol	to one and inc as only) <i>lanes:</i> - perpendicula a the reference <i>solids:</i> right regular s both planes. <i>lids:</i> s of right regu	elined t r, para planes olids- j	o othe	er plar one r pyrar U prism,	ne- Inclined eference pla <u>NIT – II</u> mid, cylinde <u>NIT – III</u>	to both the plan ane and inclined a er and cone with	es (treatme to other re axis inclin	ent is limited to ference planes - ned to one plane
lines- parallel to simple problem Projection of p Regular planes Inclined to both Projections of a Projections of a and inclined to Sections of Sol Sectional views	to one and inc as only) <i>lanes:</i> - perpendicula a the reference <i>solids:</i> right regular s both planes.	elined t r, para planes olids- j	o othe	er plar one r pyrar U prism,	ne- Inclined eference pla <u>NIT – II</u> mid, cylinde <u>NIT – III</u>	to both the plan ane and inclined a er and cone with	es (treatme to other re axis inclin	ent is limited to ference planes - ned to one plane
lines- parallel to simple problem Projection of p Regular planes Inclined to both Projections of a Projections of a and inclined to Sections of Sol Sectional views (Treatment is li Development o	to one and inc as only) <i>lanes:</i> - perpendicula a the reference <i>solids:</i> right regular s both planes. <i>lids:</i> s of right regu mited to simple <i>f Surfaces:</i>	elined t r, para planes olids- ilar sol le prob	o othe	er plar one r pyrar U prism, only)	ne- Inclined eference pla <u>NIT – II</u> mid, cylinde <u>NIT – III</u> pyramid, c	to both the plan ane and inclined the er and cone with	es (treatme to other re axis inclin	ent is limited to ference planes - led to one plane upes of Section
lines- parallel to simple problem Projection of p Regular planes Inclined to both Projections of a Projections of a and inclined to Sections of Sol Sectional views (Treatment is li Development o	to one and inc as only) <i>lanes:</i> - perpendicula a the reference <i>solids:</i> right regular s both planes. <i>lids:</i> s of right regu mited to simple <i>f Surfaces:</i>	elined t r, para planes olids- ilar sol le prob	o othe	er plar one r pyrar U prism, only)	ne- Inclined eference pla <u>NIT – II</u> mid, cylinde <u>NIT – III</u> pyramid, c	to both the plan ane and inclined the er and cone with cylinder and cone	es (treatme to other re axis inclin	ent is limited to ference planes - led to one plane upes of Section
lines- parallel to simple problem Projection of p Regular planes Inclined to both Projections of a Projections of a and inclined to Sections of Sol Sectional view (Treatment is line) Development o Development of	to one and inc as only) <i>lanes:</i> - perpendicula a the reference <i>solids:</i> right regular s both planes. <i>lids:</i> s of right regu mited to simple <i>f Surfaces:</i>	elined t r, para planes olids- ilar sol le prob	o othe	er plar one r U pyrar U prism, only) r solic	ne- Inclined eference pla <u>NIT – II</u> mid, cylinde <u>NIT – III</u> pyramid, c	to both the plan ane and inclined the er and cone with cylinder and cone	es (treatme to other re axis inclin	ent is limited to ference planes - led to one plane upes of Section
lines- parallel to simple problem Projection of p Regular planes Inclined to both Projections of a Projections of a and inclined to Sections of Sol Sectional view (Treatment is line) Development o Development of	to one and inc as only) <i>lanes:</i> - perpendicula a the reference <i>solids:</i> right regular s both planes. <i>lids:</i> s of right regu mited to simple of surfaces: of surfaces of	elined t r, para planes olids- ilar sol le prob	o othe	er plar one r U pyrar U prism, only) r solic	ne- Inclined eference pla NIT – II mid, cylinde NIT – III pyramid, c ls and their	to both the plan ane and inclined the er and cone with cylinder and cone	es (treatme to other re axis inclin	ent is limited to ference planes - led to one plane upes of Section
lines- parallel to simple problem Projection of p Regular planes Inclined to both Projections of a Projections of a and inclined to Sections of Sol Sectional views (Treatment is line Development of Cone.	to one and inc as only) <i>lanes:</i> - perpendicula a the reference <i>solids:</i> right regular s both planes. <i>lids:</i> s of right regu imited to simpl <i>f Surfaces:</i> of surfaces of	elined t r, para planes olids- ilar sol le prob right i	o othe	er plar one r U pyrar U prism, only) r solic	ne- Inclined eference pla NIT – II mid, cylinde NIT – III pyramid, c ls and their NIT – IV	to both the plan ane and inclined the er and cone with cylinder and cone	es (treatme to other re axis inclin	ent is limited to ference planes - led to one plane upes of Section
lines- parallel t simple problem Projection of p Regular planes Inclined to both Projections of s Projections of the and inclined to Sections of Sol Sectional views (Treatment is li Development of Development of cone.	to one and inc as only) <i>lanes:</i> - perpendicula a the reference <i>solids:</i> right regular s both planes. <i>lids:</i> s of right regu imited to simpl <i>f Surfaces:</i> of surfaces of	elined t r, para planes olids- ilar sol le prob right i	o othe	er plar one r pyrar prism, only) r solic un aphic v	ne- Inclined eference pla NIT – II mid, cylinde NIT – III pyramid, c ls and their NIT – IV	to both the plan ane and inclined the er and cone with cylinder and cone	es (treatme to other re axis inclin	ent is limited to ference planes - led to one plane upes of Section
lines- parallel t simple problem Projection of p Regular planes Inclined to both Projections of s Projections of the and inclined to Sections of Sol Sectional views (Treatment is li Development of Development of cone.	to one and inc as only) <i>lanes:</i> - perpendicula a the reference <i>solids:</i> right regular s both planes. <i>lids:</i> s of right regu imited to simpl <i>f Surfaces:</i> of surfaces of <i>projections:</i> pictorial views	elined t r, para planes olids- ilar sol le prob right i	o othe	er plar one r pyrar prism, only) r solic un aphic v	ne- Inclined eference pla <u>NIT – II</u> mid, cylinde <u>NIT – III</u> pyramid, c ls and their <u>NIT – IV</u> views.	to both the plan ane and inclined the er and cone with cylinder and cone	es (treatme to other re axis inclin	ent is limited to ference planes - led to one plane upes of Section
lines- parallel to simple problem Projection of p Regular planes Inclined to both Projections of a and inclined to Sections of Sol Sectional views (Treatment is li Development of Development of cone. Orthographic p conversion of p	to one and inc as only) <i>lanes:</i> - perpendicula a the reference <i>solids:</i> right regular s both planes. <i>lids:</i> s of right regu mited to simple <i>f Surfaces:</i> of surfaces of <i>projections:</i> bictorial views	elined t r, para planes olids- ilar sol le prob right i into or	o othe	er plar one r pyrar prism, only) r solic un aphic v U	ne- Inclined eference pla <u>NIT – II</u> mid, cylinde <u>NIT – III</u> pyramid, c ds and their <u>NIT – IV</u> views. <u>NIT – V</u>	to both the plan ane and inclined the er and cone with cylinder and cone	es (treatme to other re axis inclin . True sha	ent is limited to ference planes - ned to one plane upes of Section , cylinder ar

Text Books

- 1. K.L.Narayana and P.Kannaiah" Text book on Engineering Drawing," Second Edition Scitech Publications, Chennai.,2006
- 2. N.D.Bhatt and V.M.Panchal," Elementary Engineering Drawing ", 45 th Edition , Charotar Publishing house , Anand, India., 2002

Reference Books

- 1. K.Venugopal, "Engineering Drawing and Graphics with Auto CAD", Fourth Edition,2001, New Age International(P) Limited, Publishers, New Delhi, 2001
- 2. Dhananjay A Jolhe, "Engineering Drawing with an introduction to Auto CAD", Tata Mc Graw-Hill Publishing Company Ltd., New Delhi, 2008
- 3. M.B.Shaw & B.C.Rana " Engineering Drawing "Second Edition Pearson Education , New Delhi, 2009

Question Paper Pattern:

Sessional Exam

The question paper for sessional examination is for 30 marks, covering half of the syllabus for first sessional and remaining half for second sessional exam. Question Paper Contains three Either OR type questions carrying 10 marks each

End Exam

Question Paper Contains Five Either OR type questions carrying 12 marks each with one question from each unit.

ELEMENTS OF ELECTRICAL ENGINEERING (EEE)

4.3			Branc		a	1		cheme : 2017
Course Code	Category	Hou	irs/Wo	eek	Credits	N	Iaximum M	arks
EE101	Foundation	L	T	Р	С	Continuous Internal Assessment	End Exam	TOTAL
Constant of F	D	2	1	-	3	40	<u>60</u>	100
Sessional E	xam Duration :	2 Hr	. 'S			End	Exam Durat	ion: 3 Hrs
Course Out	comes : At the e	nd of	the or		tudonta wi	ll ba abla ta		
	rstand the basic					II be able to		
	rstand the constr					machinag		
	rstand the constr						nd AC Conor	atora
	rstand the basics						iu AC Uellel	at015.
	rstand the constr					,		
	Istand the consti	uction	n and (JNIT – I	lisionners		
DC Circuits:				L L				
	Current, Potent	tial L	Perieta	nce	Power and	Fnerov Sum	bol and Un	uits Ohm's las
	ws, Solution of							
	nethod and nod		,				•	
(Simple proble		0 101	tuge n		a. Bouree	indisionnation.	(elementary	fileatifient on
(Shiple prook	inis only).			I	NIT – II			
Principles of A	AC Circuits:			•				
		and r	•		1 6 .		~ ^	
	avelaye. 1.111.8	and i	naxim	um va	alue of sin	usoidal wave.	Concept of	phase and phase
	-						-	
difference. Pha	asor representati	on of	sinuso	oidal v	wave, A.C	through pure re	sistance, pur	e inductance ar
difference. Pha pure capacitan	asor representati ce, Series R-L-C	on of C Circ	sinusc uits (S	oidal v Simple	wave, A.C e Problems	through pure re). Power factor.	sistance, pur . Concept of	The inductance are $3-\Phi$ system; St
difference. Pha pure capacitan	asor representati ce, Series R-L-C nections; Voltag	on of C Circ	sinusc uits (S	oidal v Simple	wave, A.C e Problems	through pure re). Power factor.	sistance, pur . Concept of	The inductance are $3-\Phi$ system; St
difference. Pha pure capacitan and Delta con	asor representati ce, Series R-L-C nections; Voltag	on of C Circ	sinusc uits (S	oidal v Simple ent rel	wave, A.C e Problems	through pure re). Power factor.	sistance, pur . Concept of	$3-\Phi$ system; St
difference. Pha pure capacitan and Delta con	asor representati ice, Series R-L-C nections; Voltag eatment only)	on of C Circ	sinusc uits (S	oidal v Simple ent rel	wave, A.C e Problems ationship (through pure re). Power factor.	sistance, pur . Concept of	The inductance and $3-\Phi$ system; St
difference. Pha pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ	asor representati ice, Series R-L-C nections; Voltag eatment only) s: fic Induction, F iple of a DC ma	on of C Circ ge and Farada	sinuso cuits (S Curre cys La c, emf	bidal v Simple ent rel U w's, equa	wave, A.C ⁺ e Problems ationship (<u>NIT – III</u> Lenz's La tion of a 1	through pure re). Power factor, no derivation) aw and Flemin D.C Generator,	sistance, pur Concept of Problems w ngs rules. C DC motor p	e inductance ar 3-Φ system; St ith R load only Construction ar principle, voltag
difference. Pha pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ	asor representati ice, Series R-L-C nections; Voltag eatment only)	on of C Circ ge and Farada	sinuso cuits (S Curre cys La c, emf	bidal v Simple ent rel U uw's, equa ury tre	wave, A.C ⁺ e Problems ationship (<u>NIT – III</u> Lenz's La tion of a 1	through pure re). Power factor, no derivation) aw and Flemin D.C Generator,	sistance, pur Concept of Problems w ngs rules. C DC motor p	e inductance an 3-Φ system; St ith R load only Construction ar principle, voltag
difference. Pha pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ	asor representation ice, Series R-L-Connections; Voltage eatment only)	on of C Circ ge and Farada	sinuso cuits (S Curre cys La c, emf	bidal v Simple ent rel U uw's, equa ury tre	wave, A.C e Problems ationship (<u>NIT – III</u> Lenz's La tion of a l atment onl	through pure re). Power factor, no derivation) aw and Flemin D.C Generator,	sistance, pur Concept of Problems w ngs rules. C DC motor p	e inductance an 3-Φ system; St ith R load only Construction ar principle, voltag
difference. Pha pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ equation of ge Transformers	asor representation ice, Series R-L-Connections; Voltage eatment only)	on of C Circ ge and Farada achine or (ele	sinusc euits (S Curre eys La e, emf ementa	bidal v Simple ent rel U w's, equa try tre U	wave, A.C. e Problems ationship (<u>NIT – III</u> Lenz's La tion of a l atment onl <u>NIT – IV</u>	through pure re). Power factor. no derivation) aw and Flemin D.C Generator, y), (Simple Pro-	sistance, pur Concept of Problems w ngs rules. C DC motor p bblems only)	e inductance ar 3-Φ system; St rith R load only Construction ar principle, voltag
difference. Pha pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ equation of ge Transformers Working Princ	asor representati ice, Series R-L-C nections; Voltag eatment only) S: fic Induction, F iple of a DC ma nerator and moto	on of C Circ ge and Farada achine or (ele uction	sinusc euits (S Curre eys La e, emf ementa	bidal v Simple ent rel U w's, equa try tre U	wave, A.C. e Problems ationship (<u>NIT – III</u> Lenz's La tion of a l atment onl <u>NIT – IV</u>	through pure re). Power factor. no derivation) aw and Flemin D.C Generator, y), (Simple Pro-	sistance, pur Concept of Problems w ngs rules. C DC motor p bblems only)	e inductance ar 3-Φ system; St rith R load only Construction ar principle, voltag
difference. Pha pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ equation of ge Transformers Working Princ	asor representati ice, Series R-L-C nections; Voltag eatment only)	on of C Circ ge and Farada achine or (ele uction	sinusc euits (S Curre eys La e, emf ementa	bidal v Simple ent rel U w's, equa try tre U	wave, A.C. e Problems ationship (<u>NIT – III</u> Lenz's La tion of a l atment onl <u>NIT – IV</u>	through pure re). Power factor. no derivation) aw and Flemin D.C Generator, y), (Simple Pro-	sistance, pur Concept of Problems w ngs rules. C DC motor p bblems only)	e inductance an 3-Φ system; St rith R load only Construction ar principle, voltag
difference. Pha pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ equation of ge Transformers Working Princ treatment only Induction Mo	asor representati ice, Series R-L-C nections; Voltag eatment only)	on of C Circ ge and Farada achine or (ele uction ems).	sinuso cuits (S Curre ays La c, emf ementa n of 1-	oidal v Simple ent rel uw's, equa <u>ury tre</u> U	wave, A.C. e Problems ationship (<u>NIT – III</u> Lenz's La tion of a l atment onl <u>NIT – IV</u> ansformer,	through pure re). Power factor. (no derivation) aw and Flemin D.C Generator, y), (Simple Pro- transformer rat	sistance, pur Concept of Problems w ngs rules. C DC motor p bblems only)	e inductance an 3-Φ system; St vith R load only Construction ar principle, voltag
difference. Pha pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ equation of ge Transformers Working Princ treatment only Induction Mo	asor representation ice, Series R-L-Connections; Voltage eatment only) S: cic Induction, F iple of a DC manerator and moto ciple and Constr (Simple problectors: and principle of a	on of C Circ ge and Farada achine or (ele uction ems).	sinuso cuits (S Curre ays La c, emf ementa n of 1-	oidal v Simple ent rel uw's, equa <u>ury tre</u> U	wave, A.C. e Problems ationship (<u>NIT – III</u> Lenz's La tion of a l atment onl <u>NIT – IV</u> ansformer,	through pure re). Power factor. (no derivation) aw and Flemin D.C Generator, y), (Simple Pro- transformer rat	sistance, pur Concept of Problems w ngs rules. C DC motor p bblems only)	e inductance an 3-Φ system; St vith R load only Construction ar principle, voltag
difference. Pha pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ equation of ge Transformers . Working Princ treatment only Induction Mo Construction	asor representation ice, Series R-L-Connections; Voltage eatment only)	on of C Circ ge and Farada achine or (ele uction ems).	sinuso cuits (S Curre ays La c, emf ementa n of 1-	oidal v Simple ent rel uw's, equa <u>ury tre</u> U	wave, A.C. e Problems ationship (<u>NIT – III</u> Lenz's La tion of a l atment onl <u>NIT – IV</u> ansformer,	through pure re). Power factor. (no derivation) aw and Flemin D.C Generator, y), (Simple Pro- transformer rat	sistance, pur Concept of Problems w ngs rules. C DC motor p bblems only)	e inductance an 3-Φ system; St vith R load only Construction ar principle, voltag
difference. Phi pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ equation of ge Transformers Working Princ treatment only Induction Mo Construction (Theoretical as AC Generator	asor representation ice, Series R-L-Connections; Voltage eatment only)	on of C Circ ge and Farada achine or (ele uction ems).	sinuso cuits (S Curre ays La c, emf ementa n of 1-	bidal v Simple ent rel U uw's, equa ury tre U Φ Tra n of treatm	wave, A.C. e Problems ationship (<u>NIT – III</u> Lenz's La tion of a l atment onl <u>NIT – IV</u> ansformer, induction	through pure re). Power factor, no derivation) aw and Flemin D.C Generator, y), (Simple Pro- transformer rata motor, slip.	sistance, pur Concept of Problems w ngs rules. C DC motor p blems only)	e inductance an 3-Φ system; St vith R load only Construction ar principle, voltag
difference. Pha pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ equation of ge Transformers . Working Princ treatment only Induction Mo Construction (Theoretical as AC Generator Construction, 1	asor representation ice, Series R-L-Connections; Voltage eatment only) s: fice Induction, F iple of a DC mannerator and moto content of a	on of C Circ ge and Farada achine or (ele uction ems).	sinuso cuits (S Curre ays La c, emf ementa n of 1-	bidal v Simple ent rel U uw's, equa ury tre U Φ Tra n of treatm	wave, A.C. e Problems ationship (<u>NIT – III</u> Lenz's La tion of a l atment onl <u>NIT – IV</u> ansformer, induction	through pure re). Power factor, no derivation) aw and Flemin D.C Generator, y), (Simple Pro- transformer rata motor, slip.	sistance, pur Concept of Problems w ngs rules. C DC motor p blems only)	e inductance an 3-Φ system; St vith R load only Construction ar principle, voltag
difference. Phi pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ equation of ge Transformers Working Princ treatment only Induction Mo Construction (Theoretical as AC Generator Construction, T	asor representation ice, Series R-L-Conections; Voltage eatment only)	on of C Circ ce and Farada achine or (ele uction ems). of op	sinusc euits (S Curre eys La e, emf ementa n of 1- peration	bidal v Simple ent rel U w's, equa <u>uy tre</u> U Φ Tra n of <u>treatn</u>	wave, A.C. e Problems ationship ($\overline{NIT - III}$ Lenz's La tion of a latment onl $\overline{NIT - IV}$ ansformer, induction ment only) ($\overline{NIT - V}$	through pure re). Power factor. no derivation) aw and Flemin D.C Generator, y), (Simple Pro- transformer rat: motor, slip. (Theoretical asp	sistance, pur Concept of Problems w ngs rules. C DC motor p blems only) io, emf equa (elementary pects only).	re inductance ar 3-Φ system; St with R load only Construction ar principle, voltag tion. (elementar treatment only
difference. Phi pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ equation of ge Transformers . Working Princ treatment only Induction Mo Construction (Theoretical as AC Generator Construction, Illumination : Units and law	asor representation ice, Series R-L-Connections; Voltage eatment only)	on of C Circ c Circ ge and Farada achine or (ele uction ems). of op	sinuso puits (S Curre ays La e, emf ementa n of 1- peration entary pes of	bidal v Simple ent rel U w's, equa ury tre U Φ Tra n of treatm U lamps	wave, A.C. e Problems ationship ($\overline{NIT - III}$ Lenz's La tion of a latment onl $\overline{NIT - IV}$ ansformer, induction ment only) ($\overline{NIT - V}$	through pure re). Power factor. no derivation) aw and Flemin D.C Generator, y), (Simple Pro- transformer rat: motor, slip. (Theoretical asp	sistance, pur Concept of Problems w ngs rules. C DC motor p blems only) io, emf equa (elementary pects only).	re inductance an 3-Φ system; St with R load only Construction ar principle, voltag tion. (elementar treatment only
difference. Pha pure capacitan and Delta con (elementary tree DC Machines Electromagnet working princ equation of ge Transformers Working Princ treatment only Induction Mo Construction (Theoretical as AC Generator Construction, 1 Illumination: Units and law vapour lamps.	asor representation ice, Series R-L-Conections; Voltage eatment only)	on of C Circ c Circ ge and Farada achine or (ele uction ems). of op	sinuso puits (S Curre ays La e, emf ementa n of 1- peration entary pes of	bidal v Simple ent rel U w's, equa ury tre U Φ Tra n of treatm U lamps	wave, A.C. e Problems ationship ($\overline{NIT - III}$ Lenz's La tion of a latment onl $\overline{NIT - IV}$ ansformer, induction ment only) ($\overline{NIT - V}$	through pure re). Power factor. no derivation) aw and Flemin D.C Generator, y), (Simple Pro- transformer rat: motor, slip. (Theoretical asp	sistance, pur Concept of Problems w ngs rules. C DC motor p blems only) io, emf equa (elementary pects only).	re inductance ar 3-Φ system; St with R load only Construction ar principle, voltag tion. (elementar treatment only
difference. Phi pure capacitan and Delta con (elementary tre DC Machines Electromagnet working princ equation of ge Transformers Working Princ treatment only Induction Mo Construction (Theoretical as AC Generator Construction, T Illumination: Units and law vapour lamps. Earthing:	asor representation ice, Series R-L-Conections; Voltage eatment only)	on of C Circ ce and C Circ ge and C Circ farada achine or (ele uction ems). of op eleme n, Typ	sinusc suits (S Curre ays La e, emf ementa n of 1- beration entary pes of t only)	bidal v Simple ent rel U w's, equa <u>uy tre</u> U Φ Tra n of <u>treatn</u> U lamps	wave, A.C. e Problems ationship ($\overline{NIT - III}$ Lenz's La tion of a latment onl $\overline{NIT - IV}$ ansformer, induction ment only) ($\overline{NIT - V}$ s, Incandes	through pure re). Power factor. no derivation) aw and Flemin D.C Generator, y), (Simple Pro- transformer rat: motor, slip. (Theoretical asp cent lamps, Flu	sistance, pur Concept of Problems w ngs rules. C DC motor p blems only) io, emf equa (elementary pects only).	re inductance ar 3-Φ system; St rith R load only Construction ar principle, voltag tion. (elementar treatment only nps and Sodiun
difference. Pha pure capacitan and Delta con (elementary tree DC Machines Electromagnet working princ equation of ge Transformers . Working Princ treatment only Induction Mo Construction (Theoretical as AC Generator Construction, 1 Illumination: Units and law vapour lamps. Earthing: Difference bet	asor representation ice, Series R-L-Conections; Voltage eatment only)	on of C Circ ce and Farada achine or (ele uction ems). of op feleme n, Typ atment re and	sinusc suits (S Curre ays La e, emf ementa n of 1- beration entary bes of t only) d earth	bidal v Simple ent rel U w's, equa <u>ary tre</u> U Φ Tra n of <u>treatn</u> U lamps	wave, A.C. e Problems ationship ($\overline{NIT - III}$ Lenz's La tion of a la atment only $\overline{NIT - IV}$ ansformer, induction ment only) ($\overline{NIT - V}$ s, Incandes , Concept of	through pure re). Power factor, no derivation) aw and Flemin D.C Generator, y), (Simple Pro- transformer rat: motor, slip. (Theoretical asp cent lamps, Flu of earthing, app	sistance, pur . Concept of (Problems w ngs rules. C DC motor p oblems only) io, emf equa (elementary pects only).	re inductance ar 3-Φ system; St vith R load only Construction ar principle, voltag tion. (elementar treatment only nps and Sodiun fuse and MCB'
difference. Pha pure capacitan and Delta con (elementary tree DC Machines Electromagnet working princ equation of ge Transformers . Working Princ treatment only Induction Mo Construction (Theoretical as AC Generator Construction, 1 Illumination: Units and law vapour lamps. Earthing: Difference bet	asor representation ice, Series R-L-Conections; Voltage eatment only)	on of C Circ ce and Farada achine or (ele uction ems). of op feleme n, Typ atment re and	sinusc suits (S Curre ays La e, emf ementa n of 1- beration entary bes of t only) d earth	bidal v Simple ent rel U w's, equa <u>ary tre</u> U Φ Tra n of <u>treatn</u> U lamps	wave, A.C. e Problems ationship ($\overline{NIT - III}$ Lenz's La tion of a la atment only $\overline{NIT - IV}$ ansformer, induction ment only) ($\overline{NIT - V}$ s, Incandes , Concept of	through pure re). Power factor, no derivation) aw and Flemin D.C Generator, y), (Simple Pro- transformer rat: motor, slip. (Theoretical asp cent lamps, Flu of earthing, app	sistance, pur . Concept of (Problems w ngs rules. C DC motor p oblems only) io, emf equa (elementary pects only).	re inductance ar 3-Φ system; St vith R load only Construction ar principle, voltag tion. (elementar treatment only nps and Sodiun fuse and MCB'

- 1. V.K.Mehta and Rohith Mehta, "Basic electrical engineering", S.Chand publishers, 14th edition.
- 2. M.S. Naidu and S. Kamakshaiah, "Introduction to Electrical Engineering", Tata McGraw Hill Publishers, 1st edition, 2004.
- 3. B.L. Thereja, "Electrical technology-Vol-I & II", S. Chand Publishers, 23rd edition, 2004.
- 4. Dr.S.L.Uppal, "Electrical Wiring, Estimating and Costing", Khanna publishers, 1st edition, 2008.

Reference Books :

- 1. H. Cotton, "Electrical Technology", CBS Publishers, 7th edition, 2005.
- 2. Joseph Edminister, "Electric Circuits" Tata McGraw Hill Publishers, 5th edition, 2010.
- 3. K.B.Raina and S.K.Battacharya, "Electrical Design Estimating and Costing" New age publishers, 1st edition, 1991.
- 4. V.N.Mittle, "Basic electrical engineering", Tata McGraw Hill Publishers, 2nd edition, 2005.

Web References:

- 1. http://nptel.ac.in/downloads/108105053/
- 2. https://www.electrical4u.com/
- 3. http://www.smps.us/references.html
- 4. https://www.facstaff.bucknell.edu/mastascu/eLessonsHTML/EEIndex.html

E-Text Books:

- 1. http://bookboon.com/en/electrical-electronic-engineering-ebooks
- 2. http://www.freeengineeringbooks.com/Electrical/Basic-Electrical-Engineering.php

Question Paper Pattern:

Sessional Exam

The question paper for sessional examination is for 30 marks, covering half of the syllabus for first sessional and remaining half for second sessional exam. Question No 1 which carries 6 marks contains three short answer questions of two marks each. The remaining three questions shall be EITHER/OR type questions carrying 8 marks each.

End Exam

BASIC ELECTRONICS ENGINEERING (BEE)

	: Common for					1		eme : 2017
Course Code	Category	Ho	urs/W	'eek	Credits	Ν	Maximum Ma	nrks
EC101	Foundation	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
		2	1	-	3	40	60	100
Sessional H	Exam Duration	: 2 H	rs			End	Exam Duratio	on: 3 Hrs
Course Out	tcomes : At the	and a	fthaa	011#00	studente w	ill be able to		
	stand the energy						nd extrinsic se	miconductors
	lve simple probl		-				nd extrinsic se	mediatetors
	stand concepts a					n diode, BJT, F	FET and MOSI	FET
	stand basic oper							
	n various rectifie							
	he basic knowle							to solve
	s on simplificati							
CO6: Unders	tand the concept	ts of a	dders,	multi	plexers,dec	oders,flip flops	s and memory	devices.
Classification - mobility & impurities, M	or materials & t of materials bas conductivity, ass-action law, perties of Ge and	sed on Elect Charg	Energ rons a ge den	<i>ties</i> : gy Bar and H sities fect.	loles in int in semicor	rinsic semicor	nductor, Dono	r and Accepto
Classification - mobility & impurities, M electrical prop Semiconducto Open-circuite in p-n diode characteristics semiconducto diode as volta operation, per	of materials bas conductivity, ass-action law, perties of Ge and or Diodes And A d p-n junction, p d p	sed on Elect Charg I Si, H Applic D-n ju (V/I) nce, F nche ctifier	a Energ rons a ge den lall-eff ations nction chara Piecew breakd	ties: gy Bas and H sities fect. (teris ise lin lown nout fi	nd Diagram loles in int in semicon UNIT – II ctifier (forw tics of p-1 near diode & Zener br ilters)- Half	rinsic semicor nductors, Drift vard bias Reven n diode, Tem characteristics eakdown, Zen wave, Full wa	nductor, Dono current & dif rse Bias), Curr perature depe , Break down er diode chara tve, and Bridge	r and Accepto fusion currents rent component endence of V/ mechanisms in cteristics, Zene e rectifiers- the
Classification - mobility & impurities, M electrical prop Semiconducte Open-circuite in p-n diode characteristics semiconducto diode as volta operation, per	of materials bas conductivity, ass-action law, perties of Ge and or Diodes And A d p-n junction, p d p	sed on Elect Charg I Si, H Applic D-n ju (V/I) nce, F nche ctifier	a Energ rons a ge den lall-eff ations nction chara Piecew breakd	ties: gy Ba: and H isities fect. as rea cteris: ise lin lown nout fi nalysi	nd Diagram loles in int in semicon UNIT – II ctifier (forw tics of p-1 near diode & Zener br ilters)- Half	rinsic semicor nductors, Drift vard bias Reven n diode, Tem characteristics eakdown, Zen wave, Full wa	nductor, Dono current & dif rse Bias), Curr perature depe , Break down er diode chara tve, and Bridge	r and Accepto fusion currents rent component endence of V/ mechanisms in cteristics, Zene e rectifiers- the
Classification - mobility & impurities, M electrical prop Semiconducto Open-circuite in p-n diode characteristics semiconducto diode as volta operation, per diode working	of materials bas conductivity, ass-action law, perties of Ge and or Diodes And A d p-n junction, p d p	sed on Elect Charg I Si, H Applic o-n ju (V/I) nce, F nche ctifier cteris	a Energ rons a ge den lall-eff ations nction chara Piecew breakd s (with tics, an	ties: gy Bas and H ssities fect. (as red cteriss ise lin lown nout finalysi	nd Diagram loles in int in semicon UNIT – II ctifier (forw tics of p-1 near diode & Zener br ilters)- Half s and comp	rinsic semicor nductors, Drift vard bias Reven n diode, Tem characteristics eakdown, Zen wave, Full wa	nductor, Dono current & dif rse Bias), Curr perature depe , Break down er diode chara tve, and Bridge	r and Accepto fusion currents rent component endence of V/ mechanisms i cteristics, Zene e rectifiers- the
Classification - mobility & impurities, M electrical prop Semiconducto Open-circuite in p-n diode characteristics semiconducto diode as volta operation, per diode working Fundamental Construction, of configurati	of materials bas conductivity, ass-action law, perties of Ge and or Diodes And A d p-n junction, p d p	sed on Elect Charg I Si, H Applic D-n ju (V/I) nce, F nche cterist nction p-n an nd CC	a Energ rons a ge den lall-eff ations nction chara Piecew breakd s (with tics, an e Tran	ties: gy Ba: and H isities fect. as rec cteris: ise lin lown nout fin nalysi transfor -p tran gurati mpari	nd Diagram loles in int in semicor UNIT - II ctifier (forw tics of p-r near diode & Zener br ilters)- Half s and comp UNIT - III (<i>BJT</i>): nsistors, Sys- ions and the son of CB,	rinsic semicor nductors, Drift vard bias Reven n diode, Tem characteristics, eakdown, Zend wave, Full wa parison, Theore mbols, Transist eir characterist	nductor, Dono current & dif rse Bias), Curr perature depe , Break down er diode chara ive, and Bridge etical concepts tor current corr ics, Definition	r and Accepto fusion currents rent component endence of V/ mechanisms in cteristics, Zene e rectifiers- the of LED, Photo nponents, Type is of α, β, and
Classification - mobility & impurities, M electrical prop Semiconducto Open-circuite in p-n diode characteristics semiconducto diode as volta operation, per diode working Fundamental Construction, of configurati and their relat	of materials bas conductivity, ass-action law, perties of Ge and or Diodes And A d p-n junction, p d p	sed on Elect Charg I Si, H Applic D-n ju (V/I) nce, F nche cterist nction p-n an nd CC	a Energ rons a ge den lall-eff ations nction chara Piecew breakd s (with tics, an e Tran	ties: gy Ba: and H isities fect. as rec cteris: ise lin lown nout fin nalysi transfor -p tran gurati mpari	nd Diagram loles in int in semicon UNIT – II ctifier (forw tics of p-n near diode & Zener br liters)- Half s and comp <u>INIT – III</u> (<i>BJT</i>): nsistors, Sys- ions and the	rinsic semicor nductors, Drift vard bias Reven n diode, Tem characteristics, eakdown, Zend wave, Full wa parison, Theore mbols, Transist eir characterist	nductor, Dono current & dif rse Bias), Curr perature depe , Break down er diode chara ive, and Bridge etical concepts tor current corr ics, Definition	r and Accepto fusion currents rent component endence of V/ mechanisms in cteristics, Zene e rectifiers- the of LED, Photo nponents, Type is of α, β, and

$\mathbf{UNIT} - \mathbf{V}$

Digital Electronics:

Number Systems-Binary, Octal and Hexadecimal number systems, Conversions, Binary Arithmetic, Subtraction using 1's Complement & 2's Complement method, Boolean Algebra, DeMorgon's Theorems, Logic gates, Adders, Multiplexers, Decoders, Introduction to flip-flops – SR, JK, T and D flip flops, introduction to memory devices and their classification.

Text Books :

- 1. N.N Bhargava, D.C. Kulshrestha, S.C Gupta, NITTTR Chandigarh, Basic Electronics and Linear Circuits, Mc Graw Hill Education (India), Pvt. Ltd.,
- 2. Albert Paul Malvino, Electronic Principles, Mc Graw Hill International edition
- 3. Morris Mano, Digital Logic and Computer Design, PHI.

Reference Books :

- 1. Robert Boylestad. Louis Nashelsky, Electronic devices. And circuit theory., PHI
- 2. David A. Bell, Electronic Devices and Circuits, Oxford University Press, 5th edition,2008
- 3. Millman Jacob, Christos Halkias, Satyabrata Jit, Electronic Devices and Circuits, TMH

Web References:

- 1. http://www.electronics-tutorials.ws/
- 2. http://nptel.ac.in/courses/117103063/
- 3. www.electronicshub.org/tutorials/
- 4. engineering.nyu.edu/gk12/amps-cbri/pdf/Basic%20Electronics.pdf

Question Paper Pattern:

Sessional Exam

The question paper for sessional examination is for 30 marks, covering half of the syllabus for first sessional and remaining half for second sessional exam. Question No 1 which carries 6 marks contains three short answer questions of two marks each. The remaining three questions shall be EITHER/OR type questions carrying 8 marks each

End Exam

ENGINEERING MECHANICS (EGM)

I/II Semest	er: Common fo	o <mark>r all</mark> I	Branc	ehes			Sc	heme : 2017
Course Code	Category	Hou	rs/We	eek	Credits	N	laximum M	arks
CE101	Foundation	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
		2	1	-	3	40	60	100
Sessional	Exam Duration	h : 2 H	lrs			E	nd Exam Du	ration: 3 Hrs
	utcomes : At the					ill be able to		
	ulate the resultan				•			
	rmine the unknow				minate stru	ctures using equ	ilibrium con	ditions
	erstand the conce	-						
	rmine the axial for					rminate trusses		
	te the centroid of							
	rmine the momen				<u> </u>			
	pute the stresses	and st	trains	of ax	ially loaded	l members, elast	ic constants	of different
mate	rials							
	Force Systems				UNIT - I			
Equilibrium Reactions in Types of loa overhanging Static Analy Analysis of s Static Analy Friction, imp	ads, supports and beams subjected sis of Simple Pla simple trusses by sis of Systems w	anics - d bear l to dif <i>ane Tr</i> meth <i>ith Fr</i> open	ns – S fferent <i>russes</i> od of j <i>iction</i>	Suppo t type: joints frictio	UNIT - II ort reactions s of loads. and method UNIT - III on, wedge f	for simply sup	ported bean	e systems ns, cantilever and lifts by a simple
					UNIT - IV			
Area Moment of	irst moment – De nt of Inertia	s – P	aralle	l and				omposite areas. ent of inertia of
	of Deformable S	alida			U1111 - V			
Machania	j Dejormanie S		s –Sin	nple s	tresses and	strains – Types	of stresses	TT 1 1 1
Stress-strain Relation Bei	properties of ma curve for ductile tween Elastic Co	e mate nstan	erial — <i>ts</i>	Facto	or of safety	and working stre	ess.	– Hooke's law - nodulus, Rigidity

Text Books :

- 1. R.K. Bansal, "A text book of Engineering Mechanics", Laxmi Publications
- 2. B.C. Punmia, Ashok Kumar Jain and Arun Kumar Jain, "*Mechanics of materials*", Laxmi Publications.

Reference Books :

- 1. Thimoshenko & Young, "Engineering Mechanics", Tata McGraw-Hill Publications
- 2. Bhavikatti and Rajasekharappa, "Engineering Mechanics", New Age Intl. Publications
- 3. R.K.Rajput, "Applied Mechanics", Laxmi Publications.

Web References:

- 1.https//www.coursera.org
- 2.www.mathalino.com
- 3.www.nptel.ac.in/courses

Question Paper Pattern:

Sessional Exam

The question paper for sessional examination is for 30 marks, covering half of the syllabus for first sessional and remaining half for second sessional exam. Question No 1 which carries 6 marks contains three short answer questions of two marks each. The remaining three questions shall be EITHER/OR type questions carrying 8 marks each

End Exam

ENGINEERING MATHEMATICS – II (EM2)

II Semester :	Common for	all Br	anche	S			Sch	eme : 2017
Course Code	Category	Hou	rs/We	eek	Credits	Γ	Maximum Ma	nrks
BS102	Foundation	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
		2	1	-	3	40	60	100
Sessional I	Exam Duration	: 2 H	rs			End	Exam Duratio	on: 3 Hrs
Course Ou	tcomes : At the	end o	f the c	ourse	students w	ill be able to		
	e solution for s						rank of matrix	x, eigen values
and eigen vec	tors. Reduce the	e quad	ratic f	orm to	o canonical	form		
CO2: Determ	ine the Fourier	series	s of a f	unctio	on and its e	xpansion		
CO3: Unders	tand the Fourie	r trans	sforms	and Z	Z transform	S		
CO4: Utilize	Numerical Met	hods	and pr	incipl	es of least s	square methods	in engineering	5
proble								
	artial differential	-			-	paration of vari	ables in solvin	ıg
the on	e dimensional w	vave a	nd He	at equ	ations			
					UNIT - I			
Matrices					UNII - I			
Eigen values	and Eigen vec matrix. Quadrat	tors,	diagoi	naliza luctio	tion of a n n of a quad	natrix. Cayley	-Hamilton T	Statement only). heorem, finding n by orthogonal
					UNIT - II			
	n of Fourier coe		-					d Odd functions. Sine and Cosine
				τ	UNIT - III			
Transforms, I Z-Transform	ier Transforms, nverse Fourier 7 s	Fransf	orms.					ine and Cosine
	Difference equ			/11, 1 10	operites, D	imping rule, 5	linting fulc. A	
				τ	UNIT - IV			
Newton Raph		lution	of Sin	nultar	ieous Equat	tions – Gauss S	eidel iteration	

UNIT - V

Partial Differential Equations

Formation of Partial differential equations by elimination of arbitrary constants and arbitrary functions. Linear equations of first order – Lagrange's Linear equation. Applications - Method of separation of variables. One dimensional Wave equation, One dimensional Heat equation.

Text Books :

- 1. B.S. Grewal- Higher Engineering Mathematics. Khanna Publishers, 42nd Edition, 2012.
- 2. T.K.V.Iyengar and others -A Text Book of Engineering Mathematics, Vol 1-S.Chand & Company, 13th Edition 2014.

Reference Books :

- 1. B.V. Ramana -Higher Engineering Mathematics, TMH Publishers, 2nd Edition, 2006.
- 2. N.P.Bali and others -A Text Book of Engineering Mathematics, Lakshmi publishers, 7th Edition, 2009.
- 3. Erwyn Kreyszig Advanced Engineering Mathematics, John wiley, 8th Edition 2006.

Question Paper Pattern:

Sessional Exam

The question paper for sessional examination is for 30 marks, covering half of the syllabus for first sessional and remaining half for second sessional exam. Question No 1 which carries 6 marks contains three short answer questions of two marks each. The remaining three questions shall be EITHER/OR type questions carrying 8 marks each

End Exam

DATA STRUCTURES (DS)

	ommon for all B	-					Scheme	
Course Code	Category	Hou	rs/We	ek	Credits		imum Marks	5
CS103	Foundation	L	Т	Р	C	Continuous Internal Assessment	End Exam	TOTAI
C • • • • • •		3	-	-	3	40	60	<u>100</u>
Sessional Exa	m Duration : 2 H	lrs				End E	Exam Duratio	n: 3 Hrs
Course Outeer	mes : At the end of	ftha		atudar	ta will be	abla ta		
	and the purpose of							
	and the linked list							
					-			
	the operations per							
	the operations per					ire.		
CO5: Underst	and the purpose o	f struc	tures a	and file	es in C.			
				TINTEP	- T			
.				UNIT	-1			
Introduction to L		n104	хо Т :	000 07	d Non Lin-	0.7		
Definition, Classif Sequential Stora			:s, L10	ear and	LINOII LINE	ar		
-	ns on Arrays- Ins		Dele	tion 7	Fraversing	Applications of	f arrays I ine	ar Search
Binary Search, B	•				0	11	I allays-Line	al Sealei
Dinary Scarcii, D						ing of allays.		
Linked Storage F	Ponrosontation _I	inkod			· II			
Linked Storage				nters	Types of	Linked Lists	-Single linke	ed list
Doublelinked list								a not,
Doublemiked list				UNIT -	_	ing, insertion an	d Deletion.	
Linear DataStru	cturas - Stacks				• 111			
Representation o		uentia	l stora	ge and	l linked all	ocation method	ls Operations	on
Stacks- Push, Pop	• •	uentia	1 50010	ige une	i miked un	ocution method	is, operations	on
Stacks- Fush, FO	p, and Display.				TX7			
			τ	U NIT -	- IV			
Linear DataStru	ctures - Queues	auent				on Operations	on Queues- I	nsertion
<i>Linear DataStrue</i> Representation o	ctures - Queues f Queue using se	-				on, Operations	on Queues- I	nsertion,
Linear DataStru	ctures - Queues f Queue using se	-	ial and	d linke	ed allocation	on, Operations	on Queues- I	nsertion,
<i>Linear DataStrue</i> Representation o Deletion and Trav	ctures - Queues f Queue using se versing, Circular q	ueue.	ial and		ed allocation	on, Operations	on Queues- I	nsertion,
<i>Linear DataStrue</i> Representation o Deletion and Trav	ctures - Queues f Queue using se versing, Circular q a Structures-Tree	ueue.	ial and	d linko UNIT	ed allocatio	-		
<i>Linear DataStrue</i> Representation o Deletion and Trav <i>Non Linear Data</i> Basic terminolog	ctures - Queues f Queue using se versing, Circular q a Structures-Tree gy, Binary trees,	ueue. es Repres	ial and	d linke UNIT on of	ed allocatio - V Binary tree	e in memory us	sing arrays and	l linked
<i>Linear DataStrue</i> Representation of Deletion and Trav <i>Non Linear Data</i> Basic terminolog lists, Binary Se	ctures - Queues f Queue using se versing, Circular q a Structures-Tree gy, Binary trees, earch Trees, Op	ueue. s Repres	ial and	d linke UNIT on of	ed allocatio - V Binary tree	e in memory us	sing arrays and	d linked
<i>Linear DataStrue</i> Representation of Deletion and Trav <i>Non Linear Data</i> Basic terminolog lists, Binary Se	ctures - Queues f Queue using se versing, Circular q a Structures-Tree gy, Binary trees,	ueue. s Repres	ial and	d linke UNIT on of	ed allocatio - V Binary tree	e in memory us	sing arrays and	d linked
<i>Linear DataStrue</i> Representation o Deletion and Trav <i>Non Linear Data</i> Basic terminolog lists, Binary Se Traversals-Preore	ctures - Queues f Queue using se versing, Circular q a Structures-Tree gy, Binary trees, earch Trees, Op	ueue. s Repres	ial and	d linke UNIT on of	ed allocatio - V Binary tree	e in memory us	sing arrays and	d linked
<i>Linear DataStrue</i> Representation o Deletion and Trav <i>Non Linear Data</i> Basic terminolog lists, Binary Se Traversals-Preore Text Books :	ctures - Queues f Queue using se versing, Circular q a Structures-Tree gy, Binary trees, earch Trees, Op der, Inorder and P	ueue. s Repres eratior ostord	ial and sentations on er.	d linke UNIT on of binar	ed allocation - V Binary treasure y search treasure binary treasure b	e in memory us ees-Insertion,De	sing arrays and eletion and F	l linked Recursive
Linear DataStrue Representation of Deletion and Trav Non Linear Data Basic terminolog lists, Binary Se Traversals-Preore Text Books : 1. Jean Paul	<i>ctures - Queues</i> f Queue using seversing, Circular q <i>a Structures-Tree</i> gy, Binary trees, earch Trees, Op- der, Inorder and P	ueue. s Repres eratior ostord	ial and sentations on er.	d linke UNIT on of binar	ed allocation - V Binary treasure y search treasure binary treasure b	e in memory us ees-Insertion,De	sing arrays and eletion and F	l linked Recursive
Linear DataStrue Representation o Deletion and Trav Non Linear Data Basic terminolog lists, Binary Se Traversals-Preore Text Books : 1. Jean Pau Applicatio	<i>ctures - Queues</i> f Queue using seversing, Circular q <i>a Structures-Tree</i> gy, Binary trees, earch Trees, Opder, Inorder and P l Tremblay and ons, TMH.	veue. s Represertion ostord Paul	ial and sentations on er. G.Sore	d linke UNIT on of binar enson[2	ed allocatio - V Binary tre- y search tro 2007], An	e in memory us ees-Insertion,De Introduction to	sing arrays and eletion and F	l linked Recursive
Linear DataStrue Representation o Deletion and Trav Non Linear Data Basic terminolog lists, Binary Se Traversals-Preore Text Books : 1. Jean Pau Applicatio	<i>ctures - Queues</i> f Queue using seversing, Circular q <i>a Structures-Tree</i> gy, Binary trees, earch Trees, Op- der, Inorder and P	veue. s Represertion ostord Paul	ial and sentations on er. G.Sore	d linke UNIT on of binar enson[2	ed allocatio - V Binary tre- y search tro 2007], An	e in memory us ees-Insertion,De Introduction to	sing arrays and eletion and F	l linked Recursive

Reference Books :

- 1. Pradip Dey, Manas Ghosh and Reema Tereja, Computer Programming and DataStructures, Oxford University Press.
- 2. S.K.Srivatsava and Deepali Srivatsava, Data Structures through 'C' in depth, BPB Publications.

Web References :

- 1. https://www.tutorialspoint.com/data_structures_algorithms
- 2. http://www.geeksforgeeks.org/data-structures

Question Paper Pattern:

Sessional Exam

The question paper for sessional examination is for 30 marks, covering half of the syllabus for first sessional and remaining half for second sessional exam. Question No 1 which carries 6 marks contains three short answer questions of two marks each. The remaining three questions shall be EITHER/OR type questions carrying 8 marks each

End Exam

PROFESSIONAL COMMUNICATION AND ENGLISH -II (PCE - II)

II Semester :	Common for	all Br	anche	es			Sch	neme : 2017
Course Code	Category	Hou	rs/We	eek	Credits	N	Iaximum Ma	arks
HU102	Foundation	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
		3	-	-	3	40	60	100
Sessional 1	Exam Duration	: 2 H	[rs			End E	xam Duratio	on: 3 Hrs
CO 1: Write	omes: At the en Job Application Technical Repo	ns, Re	sumes	and S	Statements	of Purpose.	eports	
	Business letters	-	-		-	9	pons.	
	orehend General	,		,		Linans.		
Course Cont	ent							
	omprehension/ H	Précis	writin	σ				
U	over Letters for J			0	Resume Pr	eparation		
3. Profiling C			. 1			1		
	of Purpose for In		-		-			
U	chnical Reports	and F	ropos	als, Fo	ormats of F	Research Articles	s, Journal Pa	pers, Project
Reports	•							
6. Email Writ	0	Tormo	taofi	ottora		ttors Momos		
7. WIRING DU	isiness Letters, H	orma	15 01 L	Ruers	, DIOCK LE	uci 5,1viemos		
Reference B	ooks:							
1. Sangeeta	Sharma & Bin	od N	lishra,	Con	nmunicatio	n Skills for Ei	ngineers and	Scientists, PH
Learning Priv								
2. Marilyn A	nderson, Pramoo	1 K. N	laya a	nd Ma	adhucchand	la Sen, Critical I	Reasoning, A	cademic Writin
	ion Skills, , Pear							

3. M. Ashraf Rizvi, Effective Technical Communication, Tata McGraw-Hill Publishing Company Ltd., 2005.

4. Raymond V. Lesikar, Marie E. Flatley, "Basic Business Communication: Skills for Empowering the Internet Generation", 11th Edition, Tata McGraw-Hill. 2006.

5. Dr A. Ramakrishna Rao, Dr G. Natanam & Prof S.A. Sankaranarayanan, "English Language Communication : A Reader cum Lab Manual", Anuradha Publications, Chennai, 2006.

Question Paper Pattern:

Sessional Exam

I Sessional Examination – 30 Marks

- 1. Reading Comprehension 5M
- 2. Profiling a Company 5M
- 3. Statement of Purpose 7M
- 4. Job Application 8M
- 5. Technical Report / Project Report 5M

II Sessional Examination - 30 Marks

- 1. Email Writing 5M
- 2. Memo Writing 5M
- 3. Précis Writing 7M
- 4. Business Letter 8M
- 5. Formats of Research Articles/ Journal Papers 5 M $\,$

End Exam

- 1. Technical Report 10M
- 2. Reading Comprehension 5 Marks
- 3. Précis Writing- 5M
- 4. Job Application Letter 10M
- 5. Profiling a Company/ Business Letter 10 Marks
- 6. Statement of Purpose 10 Marks
- 7. Email/Memo Writing 10 Marks

COMPUTER PROGRAMING LAB (CPL)

Semester : Commo	n for all B	ranches	6			Scher	me: 2017
Course Code	Hours	/Week		Credits	Max	imum Marks	
CS102	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
	0	0	2	1	50	50	100
End Exam Duration	: 3 Hrs	•					
Course Outcomes :	At the end	of the c	course s	students wi	ll be able to		
CO1: Execute progr	rams using	conditio	onal and	d loop state	ements in C.		
CO2: Develop prog	rams using	g 1-Dime	ensiona	l and 2-Dir	nensional arrays.		
CO3: Perform Call	by value, C	Call by r	eferenc	ce and Recu	rsion using funct	tions	
CO4: Implement pr	ograms usi	ng poin	ters, str	ructures and	d files in C.		
			List of .	Experimen	ets		
1. Conditional Stateme	ents : Quad	ratic equ	uations	, usage of s	witch statement.		
2. Loop Statements : A	dam Num	ber, Cos	sine ser	ies			
3. Arrays : Max Min p	roblem, sta	undard d	eviatio	n and varia	nce.		
4. Character Arrays : F	Palindrome	, implen	nentatio	on of string	handling functio	ns.	
5. Functions and Recu	rsion : Mat	rix oper	ations,	Towers of	Hanoi, GCD		
6. Pointers : Interchang						ocation.	
7. Structures : Usage o	f structure	s in vari	ous app	olications.			
8. Files : File operation	ns and usag	ge of file	es in va	rious applic	cations.		
9 Assembling the hard							

9 Assembling the hardware components and installation of OS

Reference Books :1. Yashavanth P.Kanetkar , Let US C , BPB Publications, 7th Edition,2007.2. B.W. Kernignan and Dennis M.Ritchie, The C Programming Language , (PHI), 2nd Edition 2003.

APPLIED PHYSICS LAB (APP)

II Semester : Com			nches				ne: 2017		
Course Code	Hours	Week		Credits	Maximum Marks Continuous				
BS104	L	Т	Р	С	Internal Assessment	End Exam	TOTAL		
	-	-	2	1	50	50	100		
End Exam Duration	: 2 Hrs								
Course Outcomes :	At the er	d of th	e cours	e students	will be able to				
CO1: apply the kno						ndard values.			
CO2: apply the interest	-			•					
		U							
Na	te · At lea	st 12 of		of Experi llowing exi	<mark>ments</mark> periments shall l	he conducted			
1. Determination o									
2. B-H curve to stu		-		-		als			
3. Determination o	-	-			-				
4. Verification of H	Faraday's	Laws.							
5. Determination o	f wavelen	gth usi	ng a si	ngle slit.					
6. Study of magnet	tic field al	ong the	e axis o	f a circula	r coil (Steward C	Gees Apparatus)			
7. LCR Series and	Parallel F	Resonar	nce.						
8. Determination o	f wavelen	gths us	ing a g	rating.					
9. Hall Effect-dete	rmination	of Hal	l coeffi	cient and c	charge density.				
10. Determination o	f radius o	f curva	ture of	a plano-co	nvex lens using	Newton's rings.			
11. Double refraction	n - detern	ninatio	n of ref	ractive ind	ices of e-ray and	d o-ray.			
12. Determination o	f small th	ickness	by for	ming paral	lel fringes.				
13. Determination o	f rigidity	modulu	is by us	sing torsion	n pendulum.				
14. Determination o	f energy g	gap of a	semic	onductor b	y four probe me	ethod.			

ENGINEERING CHEMISTRY LABORATORY (CHP)

/ II Semester : Com				~			Scheme :20
Course Code	Ηοι	ırs/W	'eek	Credits		ximum Ma	rks
BS106	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
	-	-	2	1	50	50	100
End Exam Duration:	2 Hrs						
Course Outcomes : A	t the en	doft	he course s	tudents will	be able to		
CO1: Understand and						mentation t	hat acts as a
tools in analysis							
CO2: Understand varie		•					
CO3: Understand varie different fuels.	ous ana	lytica	l methods i	ncluding ins	trumentation that a	acts as tools	s in analysis o
				of Experime			
		ast I	2 of the foll	owing experi	iments shall be co	nducted	
Volumetric Analy							
1. Demonstration	-						
2. Preparation of s	standarc	l sodi	um carbona	ate solution.			
3. Estimation of n	nagnesi	um by	EDTA tit	ration.			
4. Estimation of c	opper b	y ED	TA titration	1.			
5. Estimation of to	otal and	perm	anent hard	ness of wate	r by EDTA titratio	on method.	
6. Estimation of c	opper ii	ı bras	s alloy.				
7. Estimation of d	issolved	l oxy	gen by Wir	nkler's metho	od.		
8. Estimation of in	on usin	g dip	hynylamine	e indicator by	y dichrometry.		
Instrumentation							
9. Determination	of calor	ific v	alue of a so	olid fuel using	g Bomb calorimet	er.	
10. Determination	of visco	sity c	of lubricatin	ıg oil using E	Engler's viscomete	er.	
11. Determination	of visco	sity c	of lubricatin	ıg oil using F	Redwood viscomet	er.	
12. Determination titrations.	of stren	gth of	f mixture of	f acids (HCl	and CH ₃ COOH) b	y conducto	metric
13. Verification of	Beer-La	ambe	rts law usin	g colorimete	er.		
14. Potentiometric	titratior	is.					
15. Determination	of simp	ارد ما	actic of two				

PHONETICS AND COMMUNICATION SKILLS LAB (PCP)

	mon for a		nches	Care ditta			ne: 2017
Course Code	Hours/	Week		Credits		laximum Mark	S
HU103	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
	0	0	2	1	50	50	100
End Exam Duration	: 2 Hrs						
	A 1	1 0 1					
Course Outcomes :						agant	
CO1: Speak internati							
CO2: Adopt appropri							
CO3: Identify Interna			-			of new words.	
CO4: Speak in Englis			-		/ely.		
CO5: Exhibit team pl	laying and	leaders	-				
			List	of Experin	nents		
Phonetics Laborator	/		· -	•			
Focus in the lab is on					· ·		
1. Introduction to Eng		tic Syn	nbols a	nd associat	ed sounds.		
2. Practice in Consona							
3. Practice in Vowels		_					
4. Practice in Accent,	Rhythm aı	nd Into	nation				
Communication Skill							
Focus in the lab is mo			n on ac	curacy			
1. Inter-personal Com a) Self Introduction	munication	1					
b) Introducing Others							
c) Non-Verbal Comm	unication						
,		<u>ao</u>					
d) Posture, gait and bo 2. Communication in 1	Formal Sit	ge.	,				
a) Public speaking – E				ech			
b) Role-play	mempore,	, i icpai	ica spe				
11							
c) Situational Dialogu	es						
c) Situational Dialogu d) Sell-out	es						
d) Sell-out	es						
d) Sell-out e) JAM							
d) Sell-out							
d) Sell-oute) JAMf) Telephone etiquette							
 d) Sell-out e) JAM f) Telephone etiquette Reference Books :		h Part	_] _ Par	t - 11 & Pa	rt - III Published	by Central Inst	itute of
 d) Sell-out e) JAM f) Telephone etiquette Reference Books : Exercises in Spol 	ken Englis				rt – III Published	by Central Inst	itute of
 d) Sell-out e) JAM f) Telephone etiquette Reference Books : Exercises in Spole English and Fore 	ken Englis eign Langu	lages, H	Hyderal	bad.		•	
 d) Sell-out e) JAM f) Telephone etiquette Reference Books : Exercises in Spote English and Fore A Course in Phore T. Balasubraman 	ken Englis eign Langu netics and	iages, H Spoken	Hyderal Englis	bad. sh, Dhami	ja Sethi, Prentice	Hall of India, F	Pvt Ltd.
 d) Sell-out e) JAM f) Telephone etiquette Reference Books : Exercises in Spol English and Fore A Course in Phore 	ten Englis Fign Langu netics and yam , A.Te	lages, H Spoken ext Boo	Hyderal Englis ok of E	bad. sh, Dhami nglish Pho	ja Sethi, Prentice netics for Indian	Hall of India, F Students, Macn	Pvt Ltd. nillan India

[/II S	emester : Comn	on for a	all brai	nches			Schen	ne: 2017
C	ourse Code	Hours	/Week		Credits	I	Maximum Marl	KS
	ME102	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
		0	0	2	1	50	50	100
End 1	Exam Duration:	3 Hrs						
Corr	rse Outcomes :	A + + h = = = =	ad af th		a atradanta	will be able to		
	To understand						carpentry house	wiring
	soldering, foun				ia equipin	ents in fitting,	carpentry, nouse	, wiring,
CO2 :	To prepare of s				ntry, fitting	g and smithy		
	To prepare sand	-		-		•		
	To do soldering							
CO5 :	To give electric	al conne	ections	in hous	se wiring.			
			T	IST C)F EXPER	RIMENTS		
Introd	luction to tools a	nd equip						
Cycle	– I (Carpentry)							
	Dovetail joint							
	Mitre-faced Bri	-						
	Mortise and Ter	non joint	t					
•	– II (Fitting)							
1.	0							
2.	Stepped fit	U						
3.	Half round	U						
•	- III (Black sm	•		•				
	Making Roun	-	are cro	ss sect	ion			
2. 3.	Making eye b Preparation of		with on	lit nigo	a nattarn			
	– IV (House wi		with sp	in piec	e pattern.			
1.			olled by	one_u	yay switch	and two-way sw	vitches	
1. 2.		lbs in se	-		-	and two-way sw	nenes.	
2. 3.				-		ase starter.		
Cycle	– IV (Soldering		I.	r	01			
1.	Soldering Prac							
2.	Soldering Resi		in Serie	es				
3.	Soldering Resi							
Stude	nt has to perform	n at lea	st two j	jobs fr	om each t	rade.		
	ence Books :	1 ** -	• •		00101 // -	** 1 1 **	1.00 2 1 2	
1.	P. Kannaiah an Publication, Ch		. Nara	yana [2010], " \	Vorkshop Manu	ial ", Second I	Edition, Scitec
2.	K.Venkata Red		3],"Firs	t year '	Workshon	manual". Bhaox	asri Publishers.	Tirupathi
	Hazrachowdhur		S.K. Bo					

DATA STRUCTURES LAB (DSP)

II Semester : Common	for all B	Branche	s			Schem	e: 2017
Course Code	Hours/	Week		Credits	Ma	ximum Marks	
CS104	L	Т	Р	С	Continuous Internal Assessment	End Exam	TOTAL
	0	0	2	1	50	50	100
End Exam Duration: 3	Hrs						
Course Outcomes : A							
CO1: Use Arrays to stor						erations.	
CO2: Understand the op	1						
CO3: Implementation of	Stack an	d queue	es using	g static and	dynamic allocati	on.	
			0	^f Experime	nts		
1. Array Data Structures		-		<u> </u>			
2. Applications of Array	Data Stru	uctures		U	•		
				0	le, Insertion, Sel		
3. Linked List: Implement			1		0		
4. Stack Data Structure:	-				· ·		tion.
	1 Imple	mentati		-	U U		
5 Queue Data Structure:	-						
5 Queue Data Structure:	-	mentati	on of (Queue opera	ations using dyna	mic allocation	
	-	mentati	on of (Queue opera	ations using dyna	mic allocation	
5 Queue Data Structure: Reference Books : 1. Yashavanth P.Kanetka	2. Imple			-	<u>_</u>	mic allocation	

2. B.W. Kernignan and Dennis M.Ritchie, The C Programming Language , (PHI), 2nd Edition 2003.